

# Chapter 7: Frequency Response

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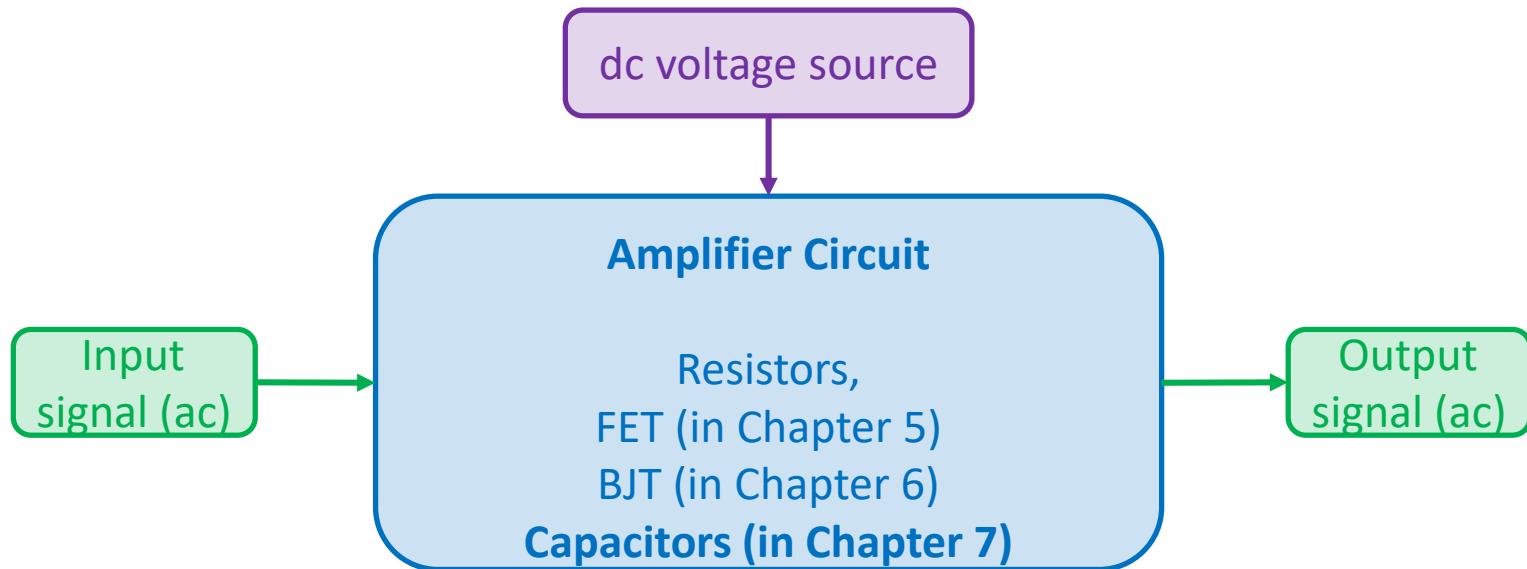
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# Preview

- Derive the **system transfer functions** of two simple RC circuits, develop the **Bode plots** for the magnitude of the transfer functions
- Discuss the general **frequency response** characteristics of amplifiers.
- Analyze the frequency response of transistor circuits with **capacitors**
- Optional: Determine the frequency response of the bipolar/MOS transistor, and determine the Miller effect and Miller capacitance.
- Optional: Determine the high-frequency response of basic transistor circuit configurations including the cascode circuit.

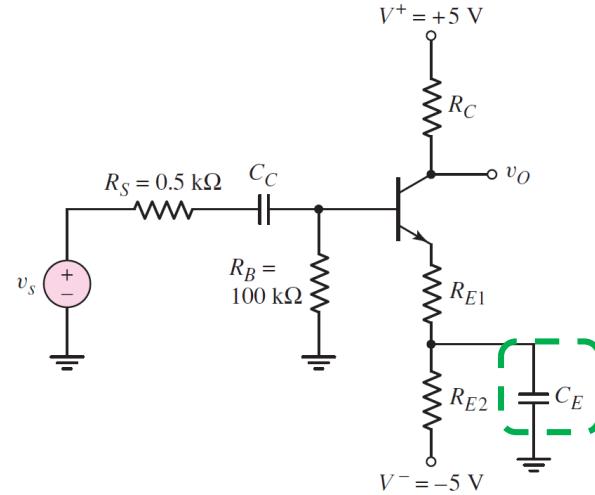
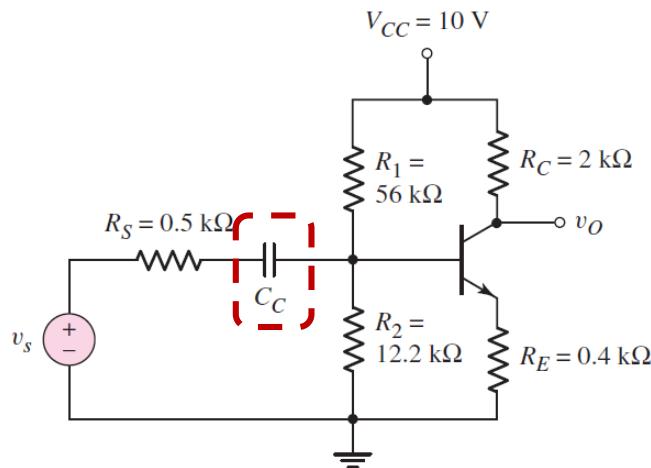
# Linear Amplifier

- FET and BJT can be used as the amplifying device



# Amplifier Gain and Frequency

- In Chapter 5 and 6, we assume the frequency of the ac signal is high enough. So, the **coupling** and **bypass** capacitors are treated as **short circuits** in ac analysis



- All **amplifier gain factors** are functions of **signal frequency**

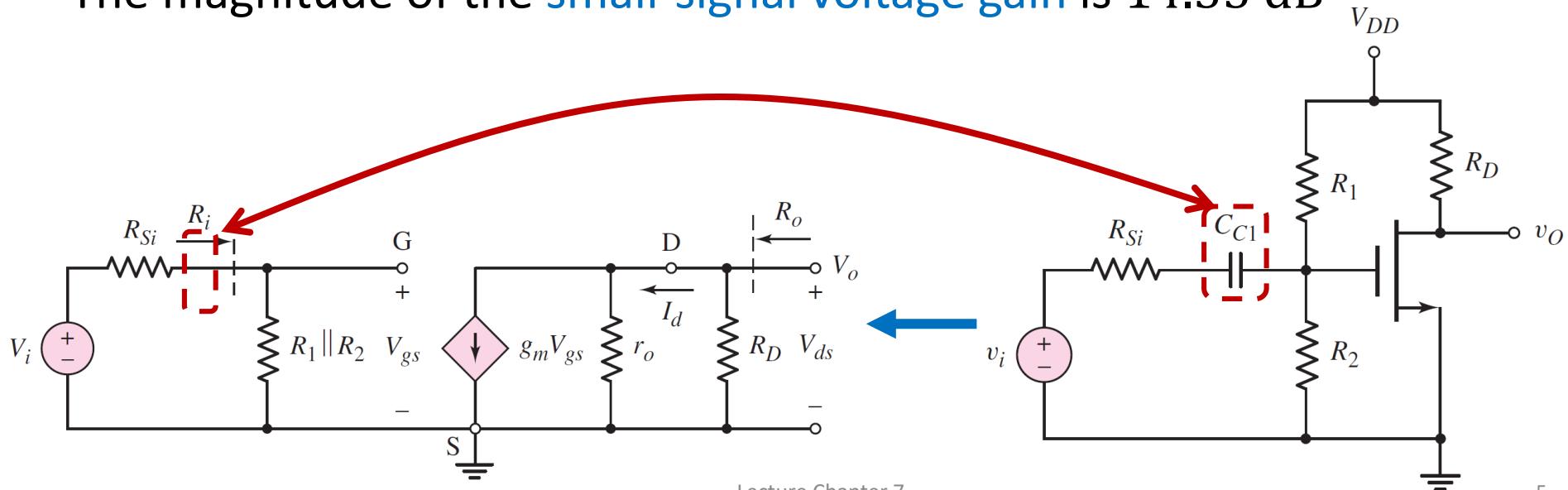
# A Quick Question on Example 4.2

- We set coupling capacitor as short circuits, then we find the **small-signal voltage gain** of this common-source amplifier circuit

$$A_v = -5.21$$

$$A_{v \text{ dB}} = 20 \log_{10} |A_v| = 20 \log_{10} (5.21) = 14.33 \text{ dB}$$

- The magnitude of the **small-signal voltage gain** is 14.33 dB



# Two Basic RC Circuits

Derive the system transfer functions of two circuits, develop the Bode diagrams of the magnitude the transfer functions, and become familiar with sketching the Bode diagrams.

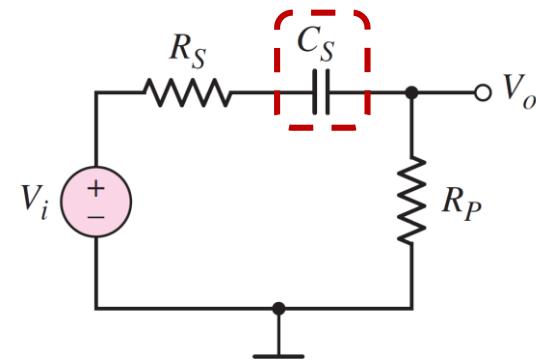
# Complex Frequency

- The frequency response of a circuit is usually determined by using the **complex frequency  $s$** 
  - $s = j\omega = j2\pi f$
  - The complex impedance of capacitor is  $\frac{1}{sC}$
  - The complex impedance of inductor is  $sL$

Name of function	Expression
<b>Voltage transfer function</b>	$T(s) = V_o(s)/V_i(s)$
Current transfer function	$T(s) = I_o(s)/I_i(s)$
Transresistance transfer function	$T(s) = V_o(s)/I_i(s)$
Transconductance transfer function	$T(s) = I_o(s)/V_i(s)$

# RC Circuit 1

- RC circuit 1: series coupling capacitor circuit
  - The capacitor  $C_S$  behaves as a **coupling capacitor**
  - $C_S$  and  $R_P$  are in series
- When  $V_i$  has zero frequency
  - The impedance of  $C_S$  is infinite → **Open Circuit**
  - $V_o = 0$
- When  $V_i$  has very high frequency
  - The impedance of  $C_S$  is very small → **Short Circuit**
  - $V_o = \frac{R_P}{R_S + R_P} V_i$



Series coupling capacitor circuit

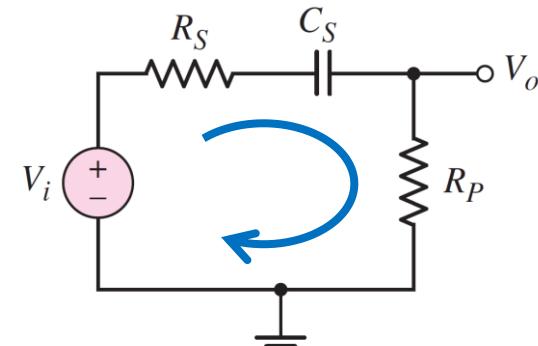
# Voltage Transfer Function

- Write a KVL equation (or a voltage divider equation) in the **loop**
- The **voltage transfer function** is

$$T(s) = \frac{V_o(s)}{V_i(s)} = \frac{R_P}{R_S + R_P + \frac{1}{sC_S}} = \frac{sR_P C_S}{1 + s(R_S + R_P)C_S} = \left( \frac{R_P}{R_S + R_P} \right) \left[ \frac{s(R_S + R_P)C_S}{1 + s(R_S + R_P)C_S} \right]$$

- $\tau_S = (R_S + R_P)C_S$  is time constant

$$T(j\omega) = K \left( \frac{j\omega\tau_S}{1 + j\omega\tau_S} \right)$$



Series coupling capacitor circuit

# Mathematical Derivation

$$T(j\omega) = \left( \frac{R_P}{R_S + R_P} \right) \left[ \frac{j\omega \tau_S}{1 + j\omega \tau_S} \right]$$

- The magnitude of  $T(j\omega)$  is

$$|T(j\omega)| = \left( \frac{R_P}{R_S + R_P} \right) \left[ \frac{\omega \tau_S}{\sqrt{1 + \omega^2 \tau_S^2}} \right] \quad |T(jf)| = \left( \frac{R_P}{R_S + R_P} \right) \left[ \frac{2\pi f \tau_S}{\sqrt{1 + (2\pi f \tau_S)^2}} \right]$$

- The magnitude of  $T(j\omega)$  in dB is:  $|T(jf)|_{\text{dB}} = 20 \log_{10} |T(jf)|$

$$\begin{aligned} |T(jf)|_{\text{dB}} &= 20 \log_{10} \left[ \left( \frac{R_P}{R_S + R_P} \right) \cdot \frac{2\pi f \tau_S}{\sqrt{1 + (2\pi f \tau_S)^2}} \right] \\ &= 20 \log_{10} \left( \frac{R_P}{R_S + R_P} \right) + 20 \log_{10}(2\pi f \tau_S) - 20 \log_{10} \sqrt{1 + (2\pi f \tau_S)^2} \end{aligned}$$

# Mathematical Derivation

$$|T(jf)|_{\text{dB}} = 20 \log_{10} \left( \frac{R_P}{R_S + R_P} \right) + 20 \log_{10}(2\pi f \tau_S) - 20 \log_{10} \sqrt{1 + (2\pi f \tau_S)^2}$$

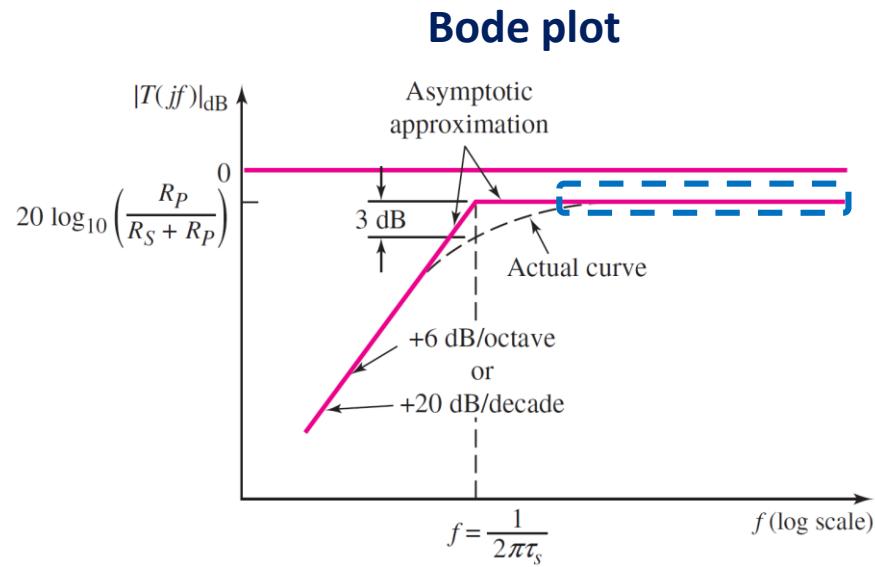
- In the first term
  - the dB value is always less than zero, as  $\frac{R_P}{R_S+R_P} < 1$
- In the second term
  - When  $f = \frac{1}{2\pi\tau_S}$ ,  $20 \log_{10}(1) = 0$
- In the third term
  - When  $f = \frac{1}{2\pi\tau_S}$ , the value is  $-3 \text{ dB} \rightarrow -20 \log_{10} \sqrt{2} = -3 \text{ dB}$
  - $f = \frac{1}{2\pi\tau_S}$  is the **break-point frequency, corner frequency or 3 dB frequency**

# Bode Plot – High Frequency

$$|T(jf)|_{\text{dB}} = 20 \log_{10} \left( \frac{R_P}{R_S + R_P} \right) + 20 \log_{10}(2\pi f \tau_S) - 20 \log_{10} \sqrt{1 + (2\pi f \tau_S)^2}$$

- When  $f \gg \frac{1}{2\pi\tau_S}$  ← corner frequency
  - $2\pi f \tau_S \approx \sqrt{1 + (2\pi f \tau_S)^2}$
  - The second and third terms cancel
- $|T(jf)|_{\text{dB}} \cong 20 \log_{10} \left( \frac{R_P}{R_S + R_P} \right) < 0$

↑  
A constant value



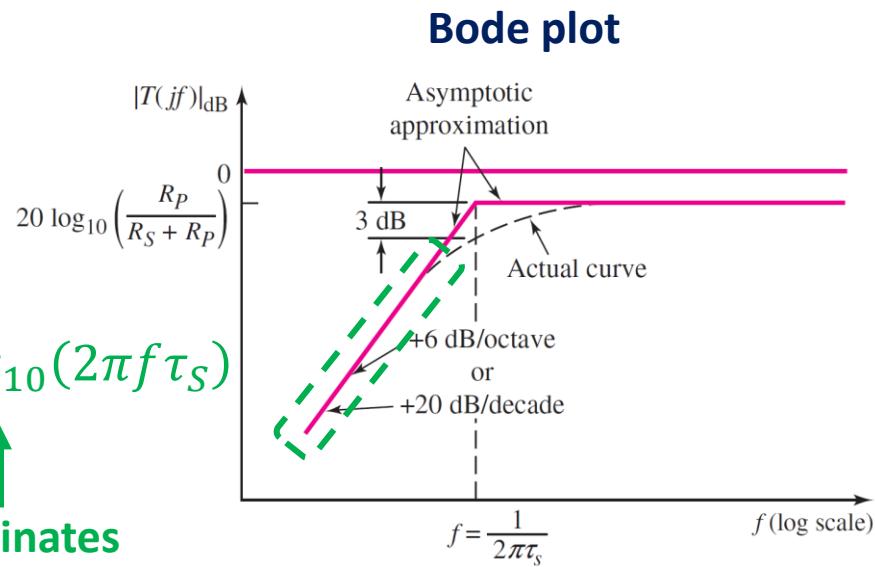
# Bode Plot – Low Frequency

$$|T(jf)|_{\text{dB}} = 20 \log_{10} \left( \frac{R_P}{R_S + R_P} \right) + 20 \log_{10}(2\pi f \tau_S) - 20 \log_{10} \sqrt{1 + (2\pi f \tau_S)^2}$$

- When  $f \ll \frac{1}{2\pi\tau_S} \leftarrow \text{corner frequency}$ 
  - $\sqrt{1 + (2\pi f \tau_S)^2} \approx 1$
  - The **third** terms is essentially 0

$$|T(jf)|_{\text{dB}} \cong 20 \log_{10} \left( \frac{R_P}{R_S + R_P} \right) + 20 \log_{10}(2\pi f \tau_S)$$

The second term **dominates**



# Bode Plot – Corner Frequency

$$|T(jf)|_{\text{dB}} = 20 \log_{10} \left( \frac{R_P}{R_S + R_P} \right) + 20 \log_{10}(2\pi f \tau_S) - 20 \log_{10} \sqrt{1 + (2\pi f \tau_S)^2}$$

- When  $f = \frac{1}{2\pi\tau_S}$  ← corner frequency

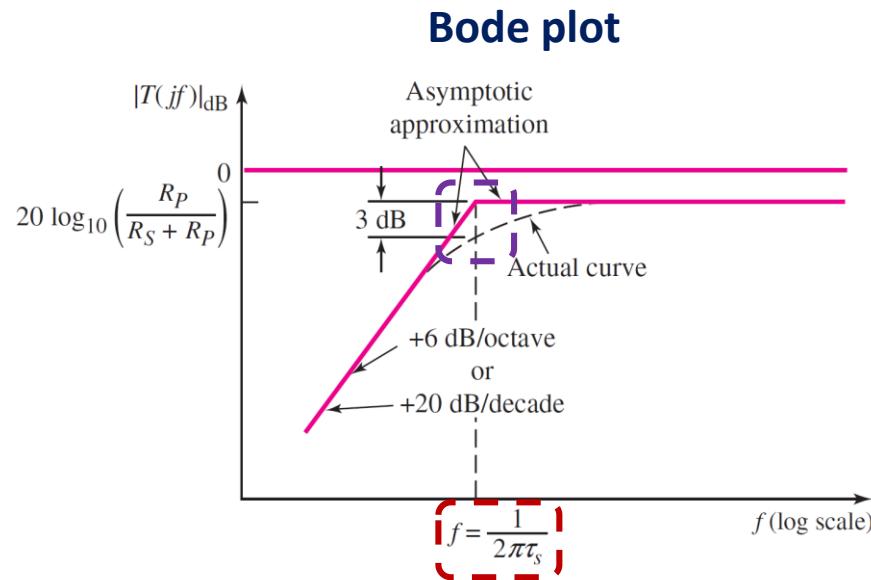
- The second terms is 0

- $20 \log_{10}(1) = 0$

- The third term is -3 dB

- $-20 \log_{10} \sqrt{2} = -3 \text{ dB}$

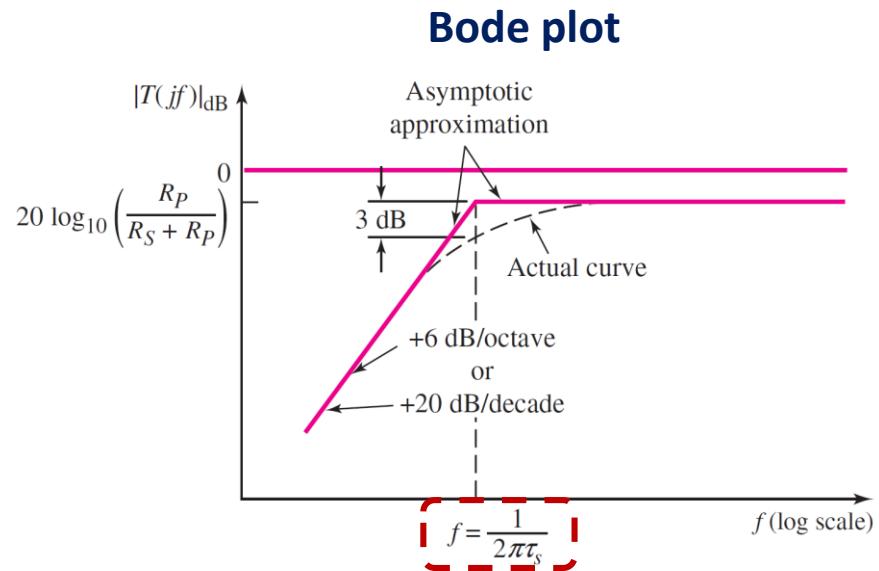
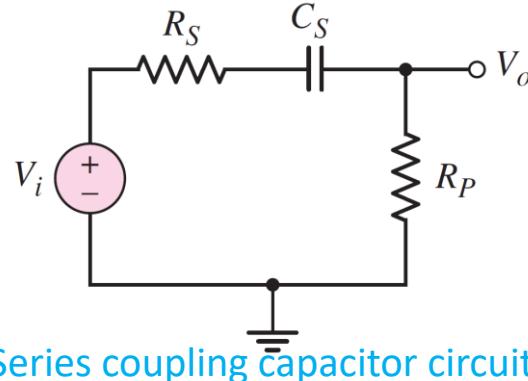
- $|T(jf)|_{\text{dB}} = 20 \log_{10} \left( \frac{R_P}{R_S + R_P} \right) - 3 \text{ dB}$



# A Quick Summary: High-Pass Network

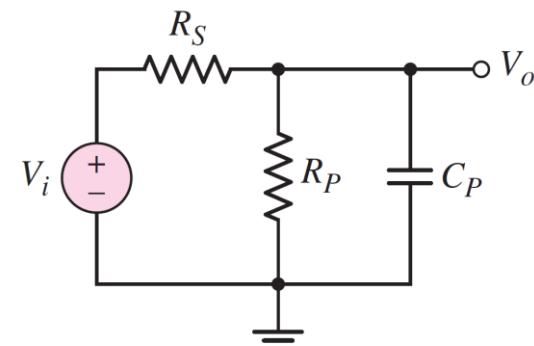
- This series coupling capacitor circuit is a **high-pass network**, since the high-frequency signals are passed through to the output

- $f = \frac{1}{2\pi\tau_s}$  is the corner frequency
- $\tau_s$  is the time constant



# RC Circuit 2

- RC circuit 2: parallel load capacitor circuit
  - $C_P$  and  $R_P$  are in parallel
  - The capacitor  $C_P$  behaves as a **load capacitor**
- When  $V_i$  has zero frequency
  - The impedance of  $C_P$  is infinite → **Open Circuit**
  - $V_o = \frac{R_P}{R_S + R_P} V_i$
- When  $V_i$  has very high frequency
  - The impedance of  $C_P$  is very small → **Short Circuit**
  - $V_o = 0$



Parallel load capacitor circuit

# Voltage Transfer Function

- Write a KCL equation in the **output node**

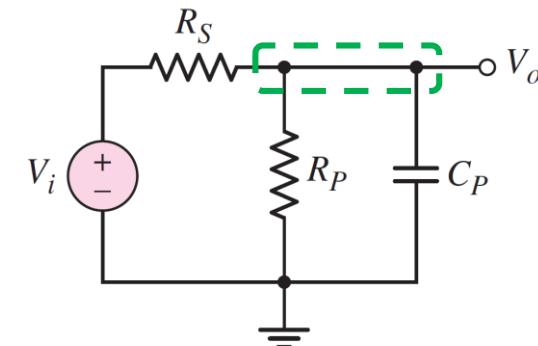
$$\frac{V_o - V_i}{R_S} + \frac{V_o}{R_P} + \frac{V_o}{(1/sC_P)} = 0$$

- The **voltage transfer function** is

$$T(s) = \frac{V_o(s)}{V_i(s)} = \left( \frac{R_P}{R_S + R_P} \right) \left[ \frac{1}{1 + s \left( \frac{R_S R_P}{R_S + R_P} \right) C_P} \right]$$

$$T(s) = \frac{V_o(s)}{V_i(s)} = \left( \frac{R_P}{R_S + R_P} \right) \left[ \frac{1}{1 + s(R_S \parallel R_P)C_P} \right] = K \left( \frac{1}{1 + s\tau_P} \right)$$

- $\tau_P$  is a time constant



Parallel load capacitor circuit

# Bode Plot: Mathematical Derivation

$$T(s) = \left( \frac{R_P}{R_S + R_P} \right) \left[ \frac{1}{1 + s\tau_P} \right]$$

$$T(jf) = \left( \frac{R_P}{R_S + R_P} \right) \left[ \frac{1}{1 + j2\pi f \tau_P} \right]$$

- The magnitude of  $T(jf)$  is

$$|T(jf)| = \left( \frac{R_P}{R_S + R_P} \right) \left[ \frac{1}{\sqrt{1 + (2\pi f \tau_P)^2}} \right]$$

- The magnitude of  $T(jf)$  in dB is:  $|T(jf)|_{\text{dB}} = 20 \log_{10} |T(jf)|$

$$|T(jf)|_{\text{dB}} = 20 \log_{10} \left( \frac{R_P}{R_S + R_P} \right) - 20 \log_{10} \sqrt{1 + (2\pi f \tau_P)^2}$$

# Mathematical Derivation

$$|T(jf)|_{\text{dB}} = 20 \log_{10} \left( \frac{R_P}{R_S + R_P} \right) - 20 \log_{10} \sqrt{1 + (2\pi f \tau_P)^2}$$

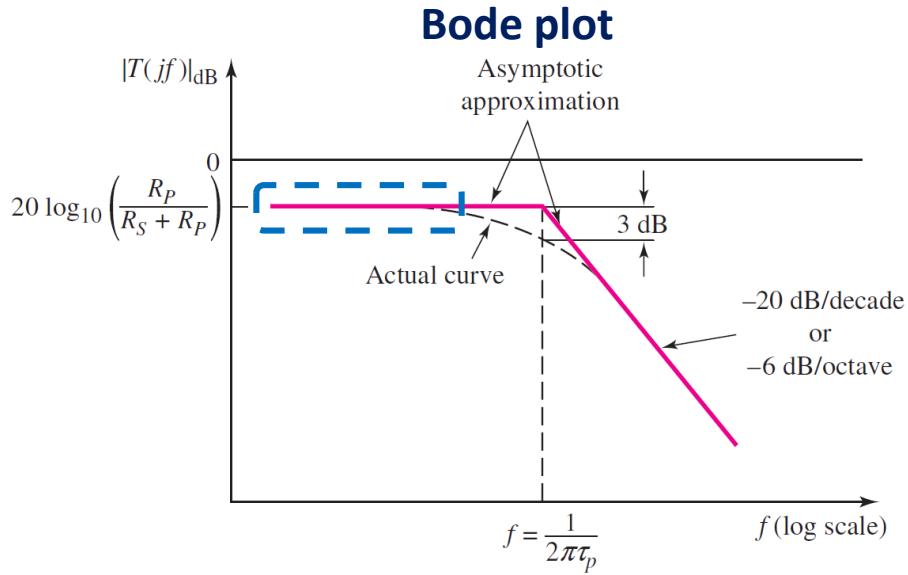
- In the first term
  - The dB value is always less than zero, as  $\frac{R_P}{R_S + R_P} < 1$  (the same with RC circuit 1)
- In the second term
  - When  $f = \frac{1}{2\pi\tau_P}$ ,  $-20 \log_{10} \sqrt{1 + 1} = -3 \text{ dB}$
  - $f = \frac{1}{2\pi\tau_S}$  is the break-point frequency, corner frequency or 3 dB frequency

# Bode Plot – Low Frequency

$$|T(jf)|_{\text{dB}} = 20 \log_{10} \left( \frac{R_P}{R_S + R_P} \right) - 20 \log_{10} \sqrt{1 + (2\pi f \tau_p)^2}$$

- When  $f \ll \frac{1}{2\pi\tau_p} \leftarrow \text{corner frequency}$ 
  - The second term is essentially zero
- $|T(jf)|_{\text{dB}} \cong 20 \log_{10} \left( \frac{R_P}{R_S + R_P} \right) < 0$

  
A constant value

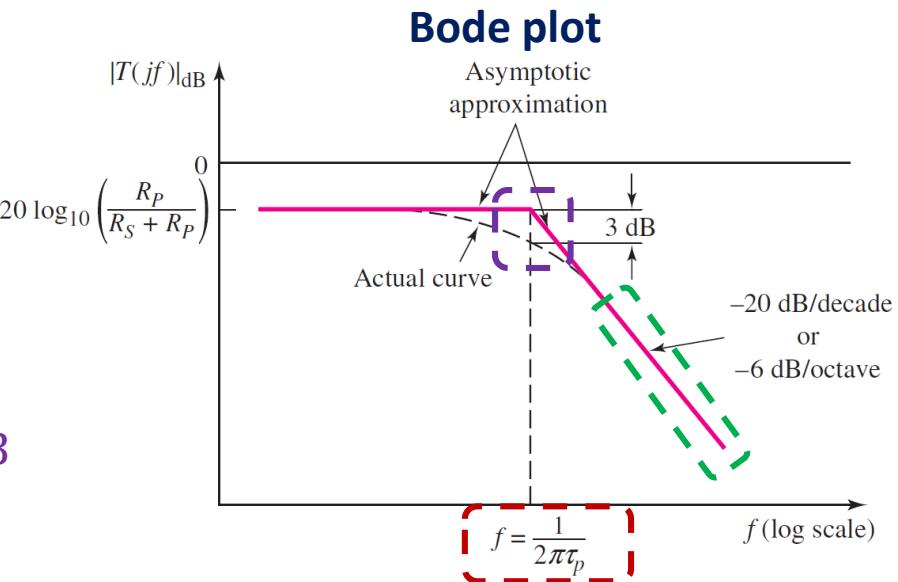


# Bode Plot – High and Corner Frequencies

$$|T(jf)|_{\text{dB}} = 20 \log_{10} \left( \frac{R_P}{R_S + R_P} \right) - 20 \log_{10} \sqrt{1 + (2\pi f \tau_p)^2}$$

- When  $f \gg \frac{1}{2\pi\tau_p}$  ← corner frequency
  - The second term dominates
- When  $f = \frac{1}{2\pi\tau_p}$ 
  - The second term is -3 dB

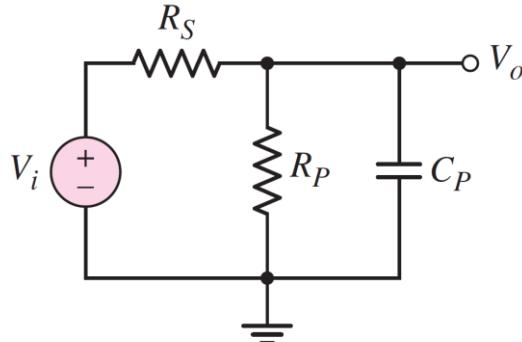
$$|T(jf)|_{\text{dB}} = 20 \log_{10} \left( \frac{R_P}{R_S + R_P} \right) - 3 \text{ dB}$$



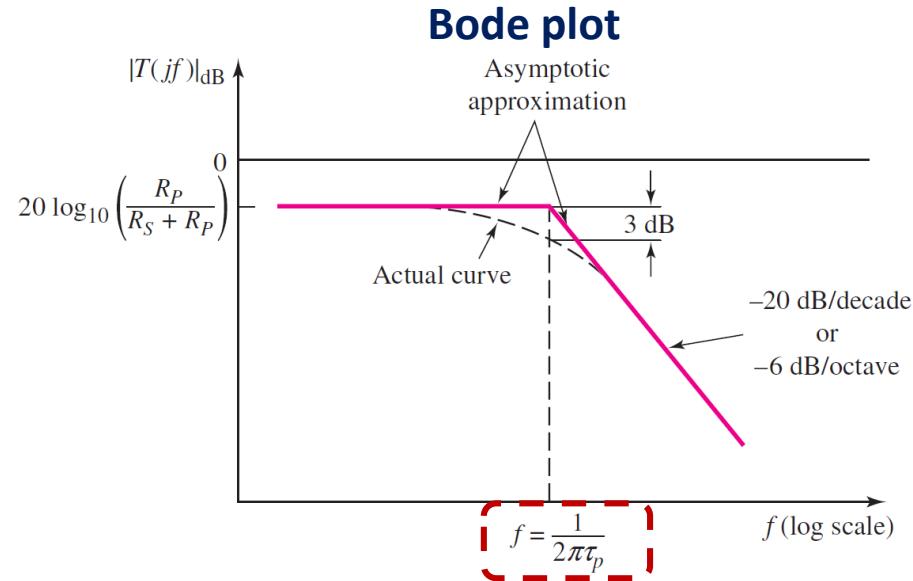
# A Quick Summary: Low-Pass Network

- The parallel load capacitor circuit is called a **low-pass network**, since the low-frequency signals are passed through to the output

- $f = \frac{1}{2\pi\tau_P}$  is the corner frequency
- $\tau_P$  is the time constant



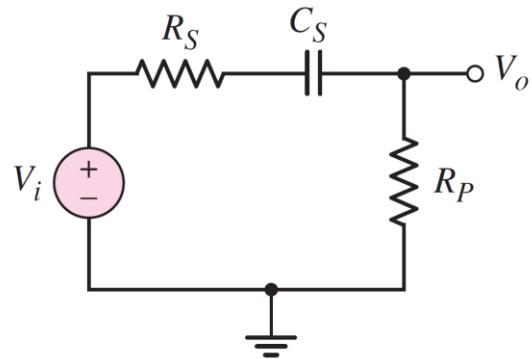
Parallel load capacitor circuit



# Example 7.1

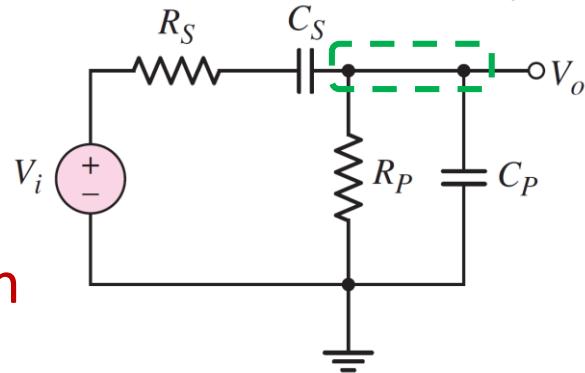
Determine the corner frequency and Bode plot for the circuit.

Assume  $R_S = 1 \text{ k}\Omega$ ,  $R_P = 10 \text{ k}\Omega$ ,  $C_S = 1 \mu\text{F}$ .



# Short-Circuit and Open-Circuit Time Constants

- Combine the **RC circuit 1** and the **RC circuit 2**
  - The circuit with two capacitors
  - $C_S$  is the **coupling capacitor**
  - $C_P$  is the **load capacitor**
- We can determine the **voltage transfer function** by writing a **KCL equation** at the **output node**



$$\frac{V_o - V_i}{R_S + \frac{1}{sC_S}} + \frac{V_o}{R_P} + \frac{V_o}{sC_P} = 0$$

$$V_i \left( \frac{1}{R_S + \frac{1}{sC_S}} \right) = V_o \left( \frac{1}{R_S + \frac{1}{sC_S}} + \frac{1}{R_P} + \frac{1}{sC_P} \right)$$

# Open- and Short-Circuit Time Constants

- The result is

$$T(s) = \frac{V_o(s)}{V_i(s)} = \frac{1}{R_S + \frac{1}{sC_S} \left( \frac{1}{R_S + \frac{1}{sC_S}} + \frac{1}{R_P} + \frac{1}{sC_P} \right)} = \frac{1}{\frac{R_S + R_P}{R_P} + \frac{1}{sC_S R_P} + sC_P R_S + \frac{C_P}{C_S}}$$

$$T(s) = \frac{V_o(s)}{V_i(s)} = \frac{R_P}{R_S + R_P} \times \frac{1}{1 + \frac{1}{sC_S R_P} \frac{R_P}{R_S + R_P} + sC_P R_S \frac{R_P}{R_S + R_P} + \frac{R_P}{R_S + R_P} \frac{C_P}{C_S}}$$

$$T(s) = \frac{V_o(s)}{V_i(s)} = \frac{R_P}{R_S + R_P} \times \frac{1}{1 + \frac{1}{s\tau_S} + s\tau_P + \frac{R_P}{R_S + R_P} \frac{C_P}{C_S}}$$

# Open- and Short-Circuit Time Constants

- The **voltage transfer function** of the circuit is

$$T(s) = \frac{V_o(s)}{V_i(s)} = \frac{R_P}{R_S + R_P} \times \frac{1}{1 + \frac{1}{s\tau_S} + s\tau_P + \frac{R_P}{R_S + R_P} \frac{C_P}{C_S}}$$

- Usually,  $C_P \ll C_S$

- At low frequencies,  $C_P$  was made an open circuit

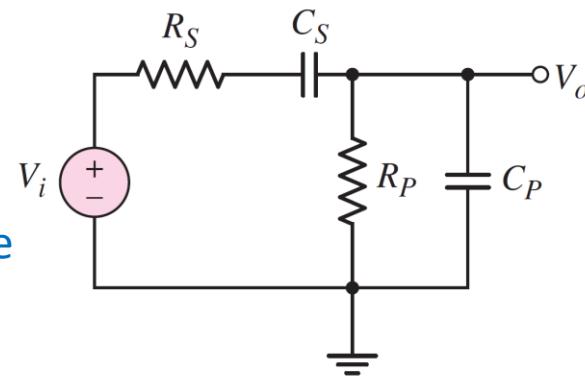
- $\tau_S$  is called an **open-circuit time constant**

- $\tau_S = C_S(R_S + R_P)$ ,  $R_S + R_P$  is the **effective resistance** seen by the capacitor  $C_S$

- At high frequencies,  $C_S$  was made a short circuit

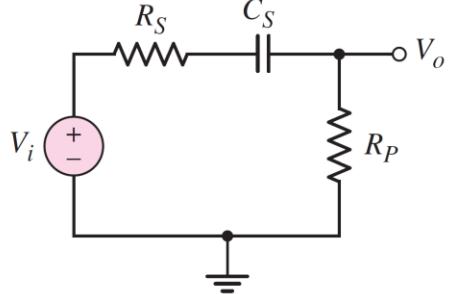
- $\tau_P$  is called a **short-circuit time constant**

- $\tau_P = C_P(R_S \parallel R_P)$ ,  $R_S \parallel R_P$  is the **effective resistance** seen by the capacitor  $C_P$

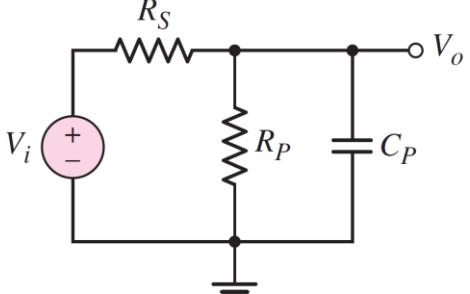


# Bode Plot and Corner Frequencies

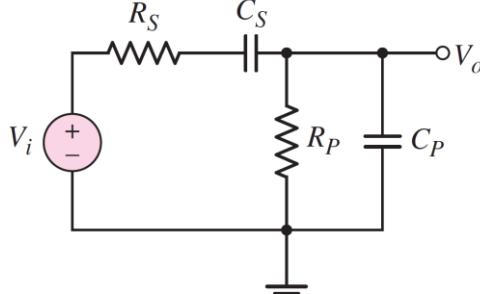
- Combine the **high-pass** and **low-pass** networks



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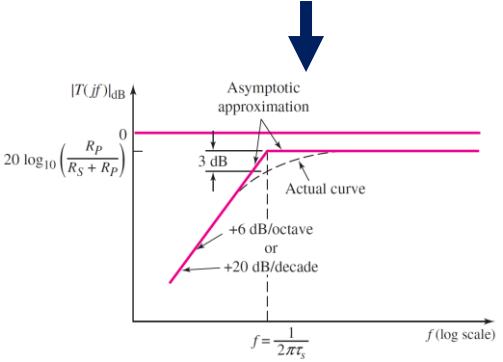
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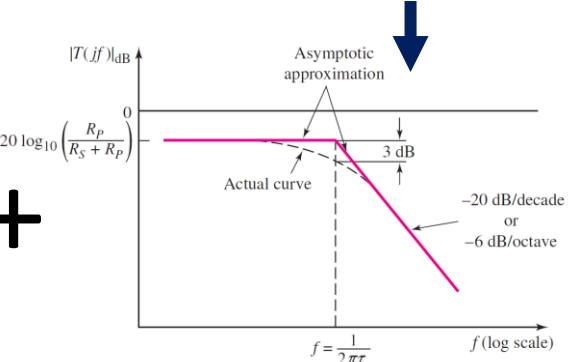
Series coupling capacitor circuit  
(high-pass network)

Parallel load capacitor circuit  
(low pass network)

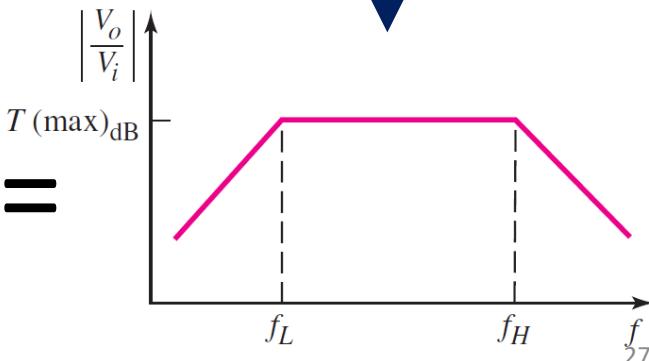
**Bode plot**



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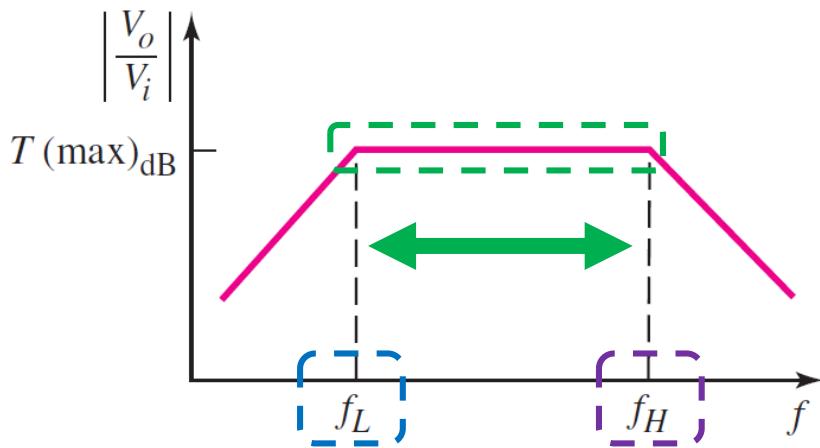


Lecture Chapter 7



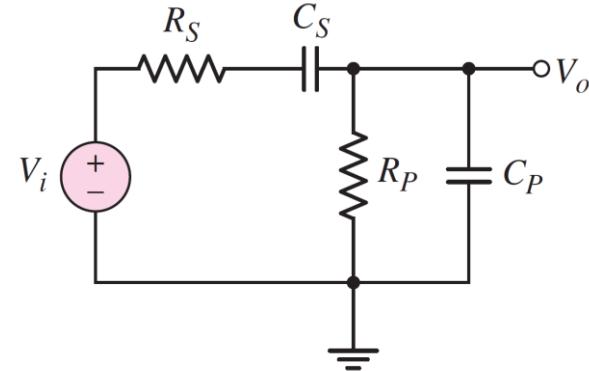
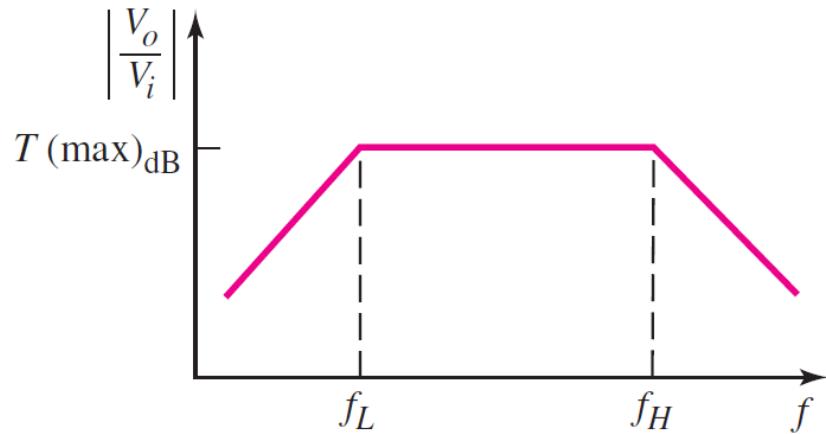
# Bode Plot and Corner Frequencies

- The corner frequencies of the Bode plot
  - Lower corner frequency,  $f_L = \frac{1}{2\pi\tau_S}$
  - Upper corner frequency,  $f_H = \frac{1}{2\pi\tau_P}$
- The mid-band range, or the bandwidth is  $f_{BW} = f_H - f_L \cong f_H$



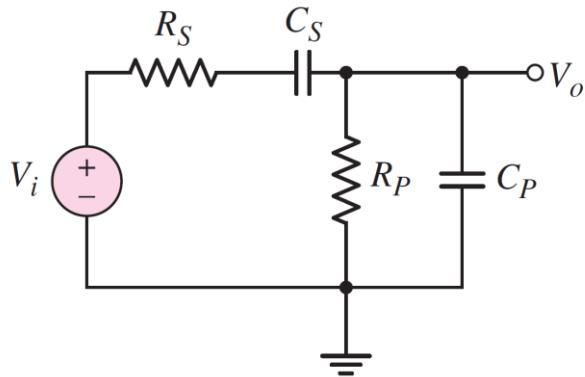
# Bode Plot and Corner Frequencies

- At the high end of the frequency spectrum
  - The voltage transfer function magnitude decreases because the **load capacitor** does not act as perfect open circuit
- At the low end of the frequency spectrum
  - The voltage transfer function magnitude decreases because **coupling capacitor** does not act as perfect short circuit



# Example 7.2

Determine the corner frequencies and bandwidth of a passive circuit containing two capacitors. Assume  $R_S = 1 \text{ k}\Omega$ ,  $R_P = 10 \text{ k}\Omega$ ,  $C_S = 1 \mu\text{F}$ ,  $C_P = 3 \text{ pF}$ .

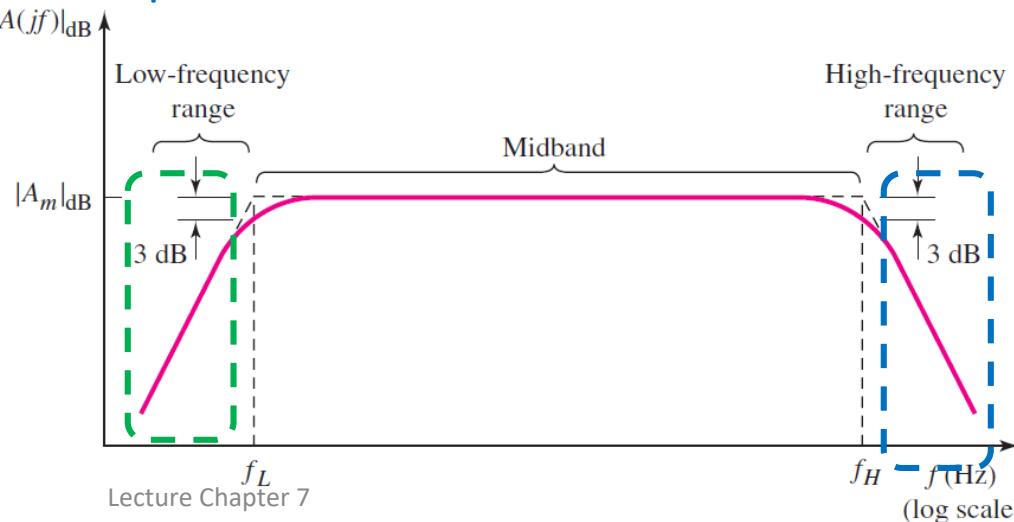


# Frequency Response: Transistor Amplifiers with Circuit Capacitors

Analyze the frequency response of transistor circuits with capacitors.

# Amplifier Gain and Frequency

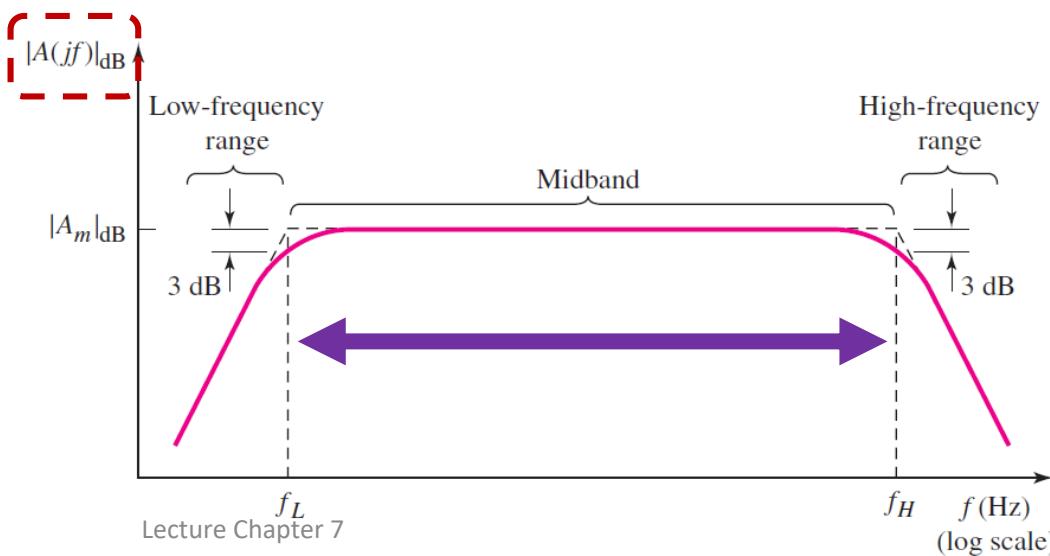
- The Bode plots for transistor amplifiers are similar to RC circuits
- When the source frequency is low:  $f < f_L$ 
  - Coupling and bypass capacitor effects ()
- When the source frequency is high:  $f > f_H$ 
  - Stray capacitance and transistor capacitance effects



# Amplifier Gain and Frequency

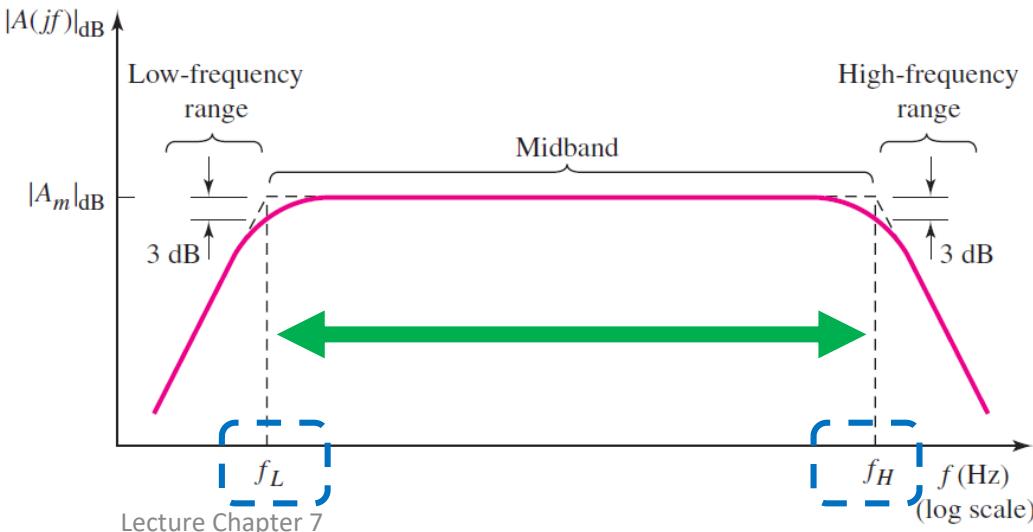
- In the mid-band range:  $f_L < f < f_H$ 
  - Coupling and bypass capacitors act as short circuits
  - Load capacitor, stray and transistor capacitances act as open circuits
- The small-signal voltage gain we determined in Chapter 5 and 6 is the mid-band gain
- The amplifier gain is also plotted in terms of **decibels (dB)**

$$|A|_{\text{dB}} = 20 \log_{10} |A|$$



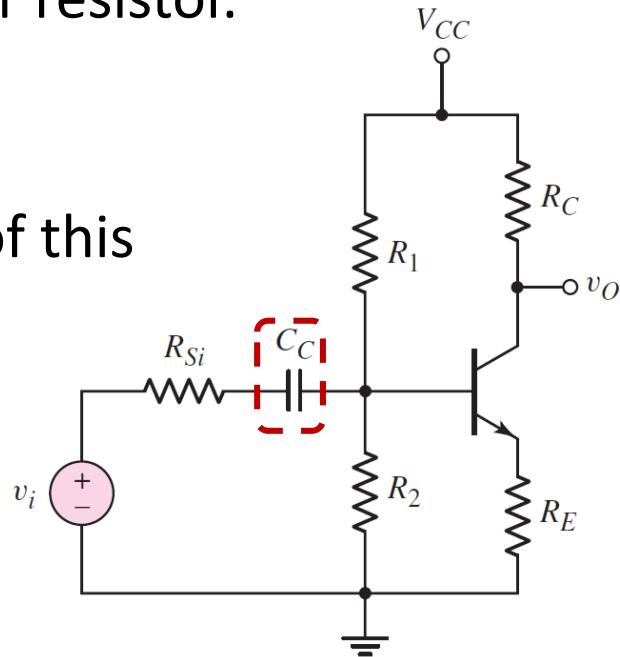
# Amplifier Gain and Frequency

- Corner frequency
  - The gain at  $f = f_L$  and  $f = f_H$  is 3 dB less than the mid-band gain ( $|A|_{\text{dB}}$ )
- The **bandwidth** of the amplifier is defined as
  - $f_{\text{BW}} = f_H - f_L$



# Transistor Amplifiers with Capacitors

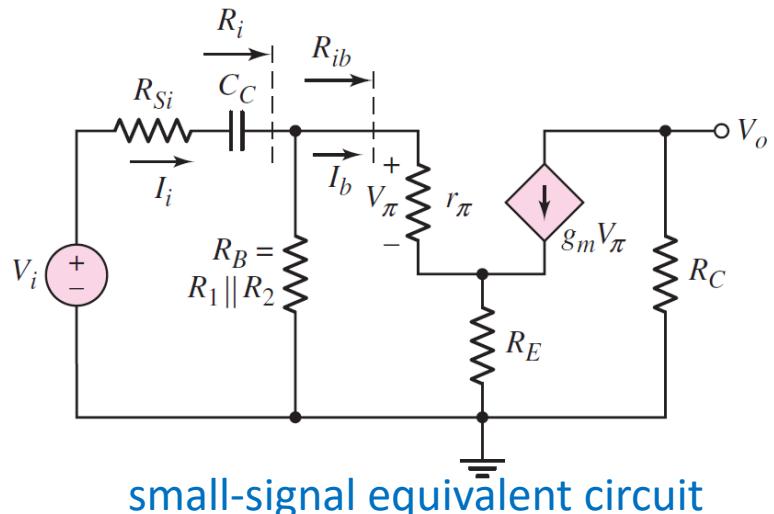
- Three types of capacitors will be considered in this Chapter
  - Coupling capacitor, load capacitor, and bypass capacitor
- This is a common-emitter circuit with emitter resistor.  $C_C$  is the **input coupling capacitor**
- What is the general shape of the **Bode plot** of this amplifier circuit?
  - High pass network or low pass network?



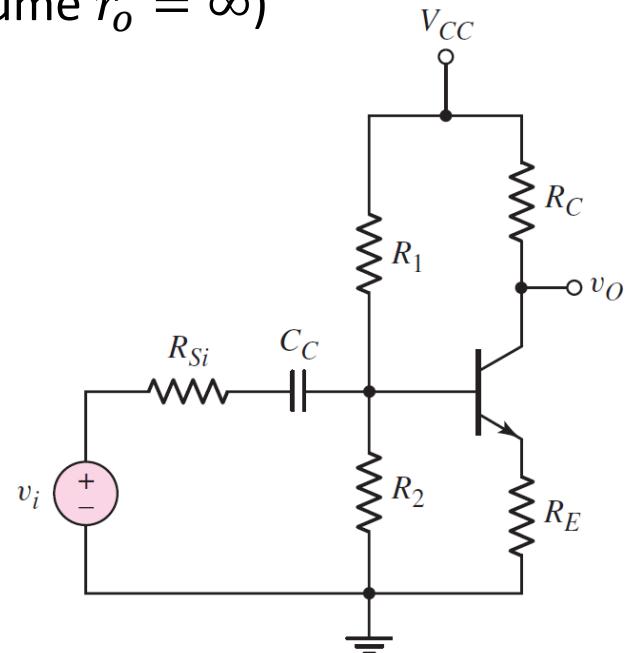
# Common-Emitter Circuit with Coupling Capacitor

- Draw the small-signal equivalent circuit

- Set all dc sources to zero
- Replace the BJT by the hybrid- $\pi$  model (assume  $r_o = \infty$ )
- Keep the coupling capacitor in the circuit

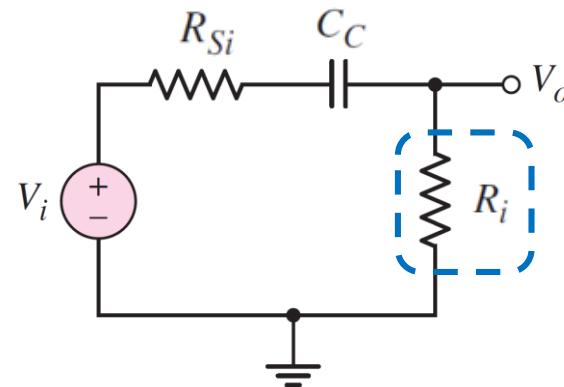
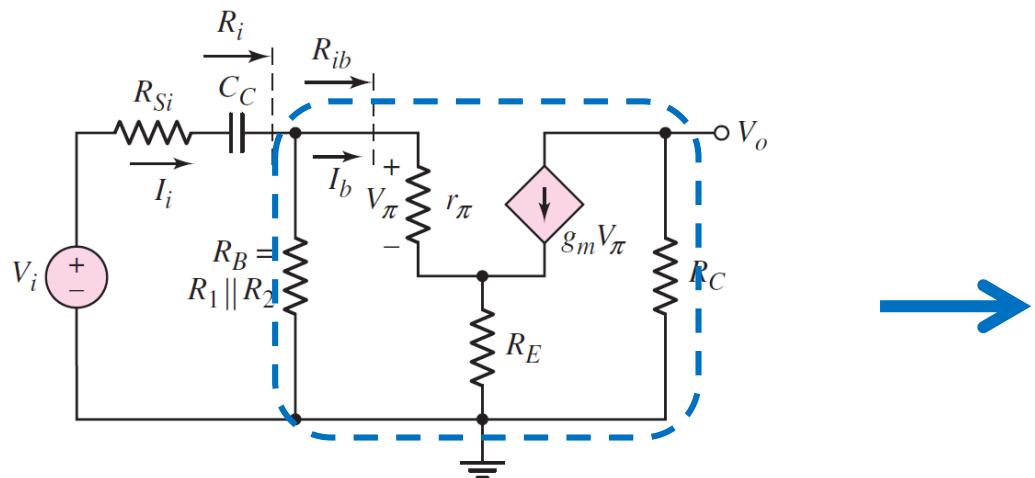


Lecture Chapter 7



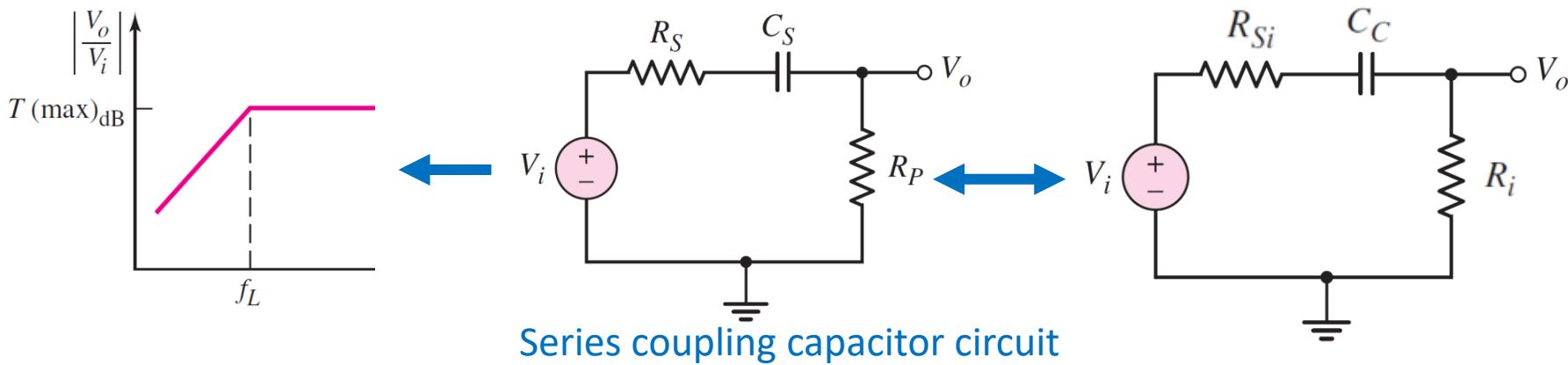
# Common-Emitter Circuit with Coupling Capacitor

- The input resistance of the circuit is
  - $R_i = R_1 \parallel R_2 \parallel R_{ib}$
  - $R_{ib} = r_\pi + (1 + \beta)R_E$
  - See Chapter 6 contents for more details...



# Common-Emitter Circuit with Coupling Capacitor

- This common-emitter circuit is equivalent to a **series coupling capacitor circuit** (RC circuit 1)
- We note that this common-emitter circuit is a **high-pass network**



# Bode Plot of a Common-Emitter Circuit

- To find the **small-signal voltage gain**, considering **coupling capacitor**

- $$A_v(s) = \frac{V_o(s)}{V_i(s)}$$

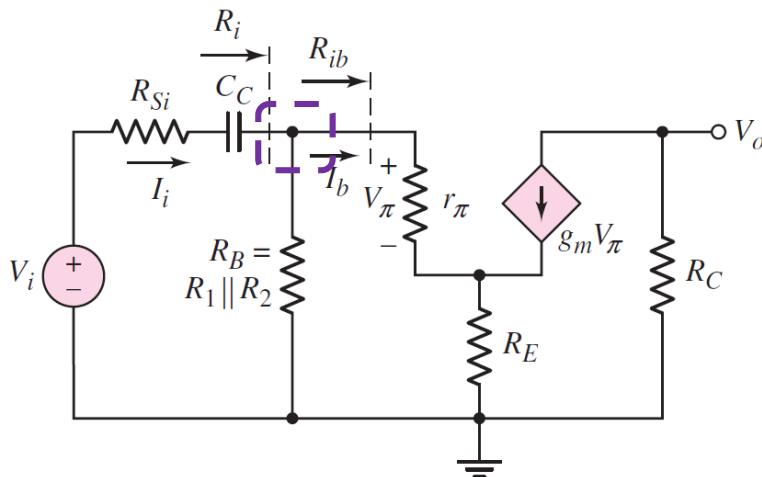
- $$V_o \leftrightarrow V_\pi \leftrightarrow I_b \leftrightarrow I_i \leftrightarrow V_i$$

- The output voltage is

$$V_o = -g_m V_\pi R_C = -g_m (I_b r_\pi) R_C$$

- Write a current divider equation in the **base node**

$$I_b = \left( \frac{R_B}{R_B + R_{ib}} \right) I_i$$



# Bode Plot of a Common-Emitter Circuit

- The input current is

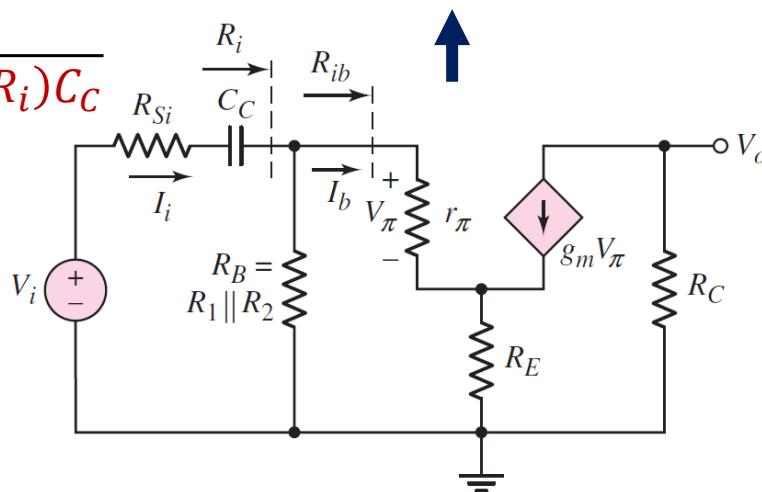
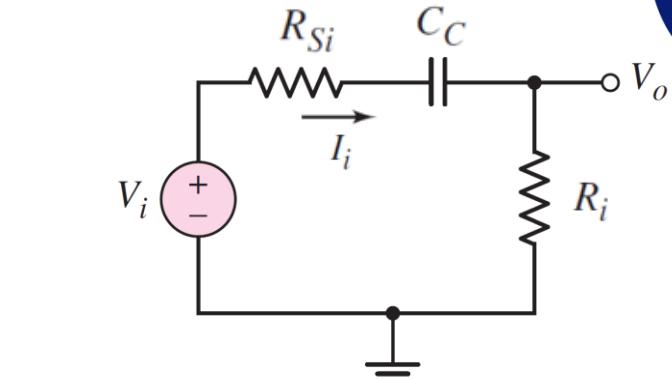
$$I_i = \frac{V_i}{R_{Si} + \frac{1}{sC_C} + R_i}$$

- The small-signal voltage gain is

$$A_v(s) = \frac{V_o(s)}{V_i(s)} = -g_m r_\pi R_C \left( \frac{R_B}{R_B + R_{ib}} \right) \frac{sC_C}{1 + s(R_{Si} + R_i)C_C}$$

$$A_v(s) = \frac{V_o(s)}{V_i(s)} = \frac{-g_m r_\pi R_C}{(R_{Si} + R_i)} \left( \frac{R_B}{R_B + R_{ib}} \right) \frac{s\tau_s}{1 + s\tau_s}$$

We have got this result in Chapter 6

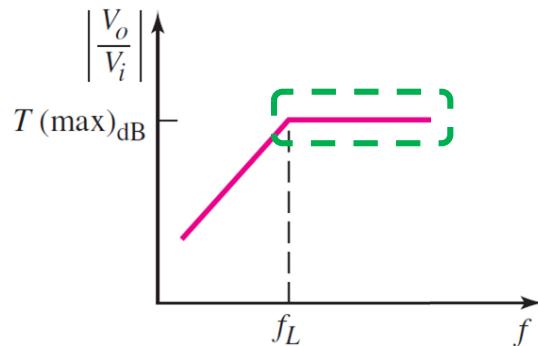


# Bode Plot of a Common-Emitter Circuit

$$A_v(s) = \frac{V_o(s)}{V_i(s)} = \frac{-g_m r_\pi R_C}{(R_{Si} + R_i)} \left( \frac{R_B}{R_B + R_{ib}} \right) \frac{s\tau_s}{1 + s\tau_s}$$

- The maximum gain can be achieved when the signal has very high frequency
- The **maximum** magnitude of the small-signal voltage gain, in **decibels**, is

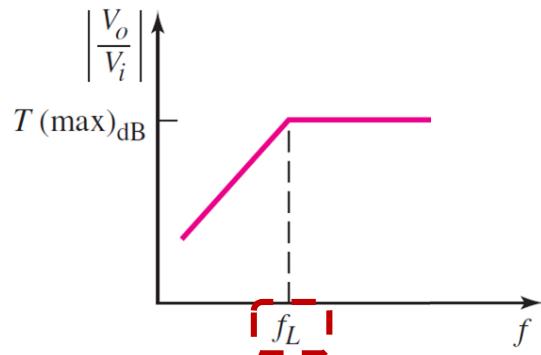
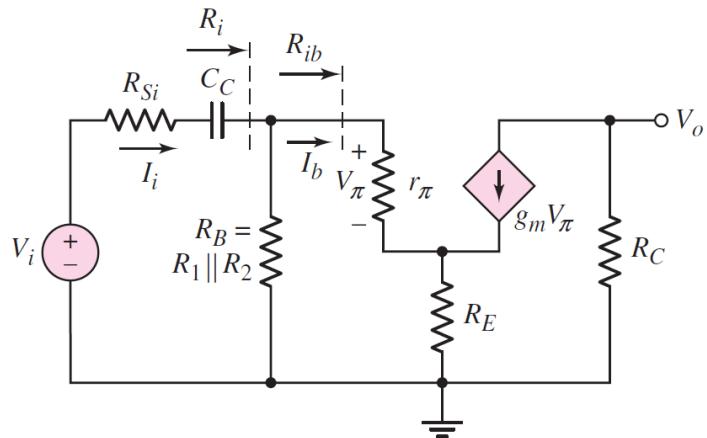
$$\begin{aligned} |A_v(\max)|_{\text{dB}} &= 20 \log_{10} |A_v(\max)| \\ &= 20 \log_{10} \frac{g_m r_\pi R_C}{(R_{Si} + R_i)} \left( \frac{R_B}{R_B + R_{ib}} \right) \end{aligned}$$



# Bode Plot of a Common-Emitter Circuit

- The effective resistance seen by the coupling capacitor is  $R_{Si} + R_i$
- The lower corner frequency is

$$f_L = \frac{1}{2\pi\tau_S} = \frac{1}{2\pi(R_{Si} + R_i)C_C}$$

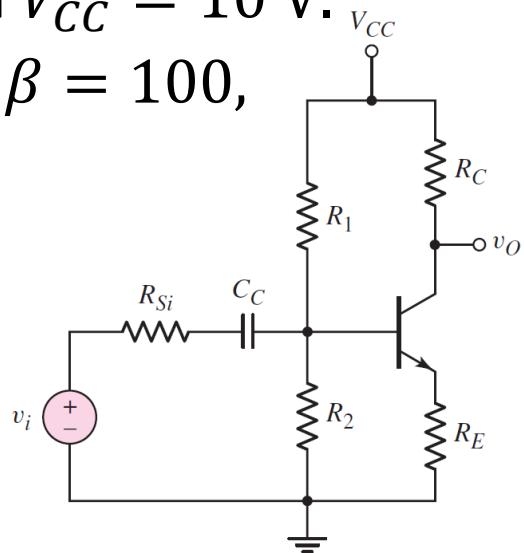


# Example 7.3

Calculate the corner frequency and maximum gain of a bipolar common-emitter circuit with a coupling capacitor.

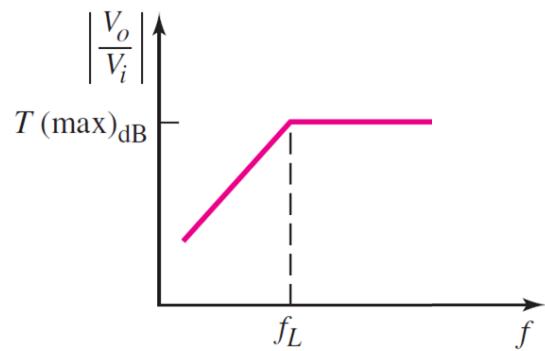
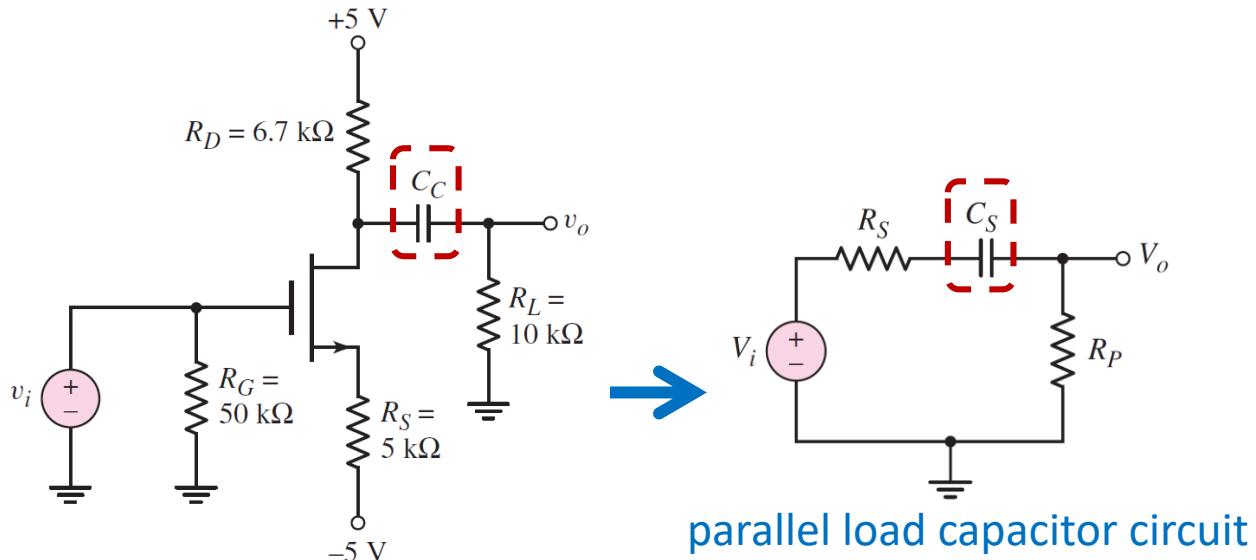
The parameters are:  $R_1 = 51.2 \text{ k}\Omega$ ,  $R_2 = 9.6 \text{ k}\Omega$ ,  $R_C = 2 \text{ k}\Omega$ ,  $R_E = 0.4 \text{ k}\Omega$ ,  $R_{Si} = 0.1 \text{ k}\Omega$ ,  $C_C = 1 \mu\text{F}$ , and  $V_{CC} = 10 \text{ V}$ .

The transistor parameters are:  $V_{BE}(\text{on}) = 0.7 \text{ V}$ ,  $\beta = 100$ , and  $V_A = \infty$ .



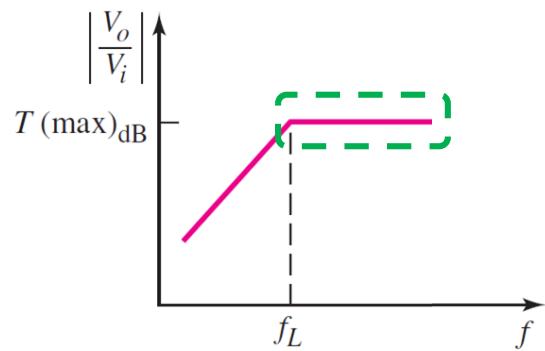
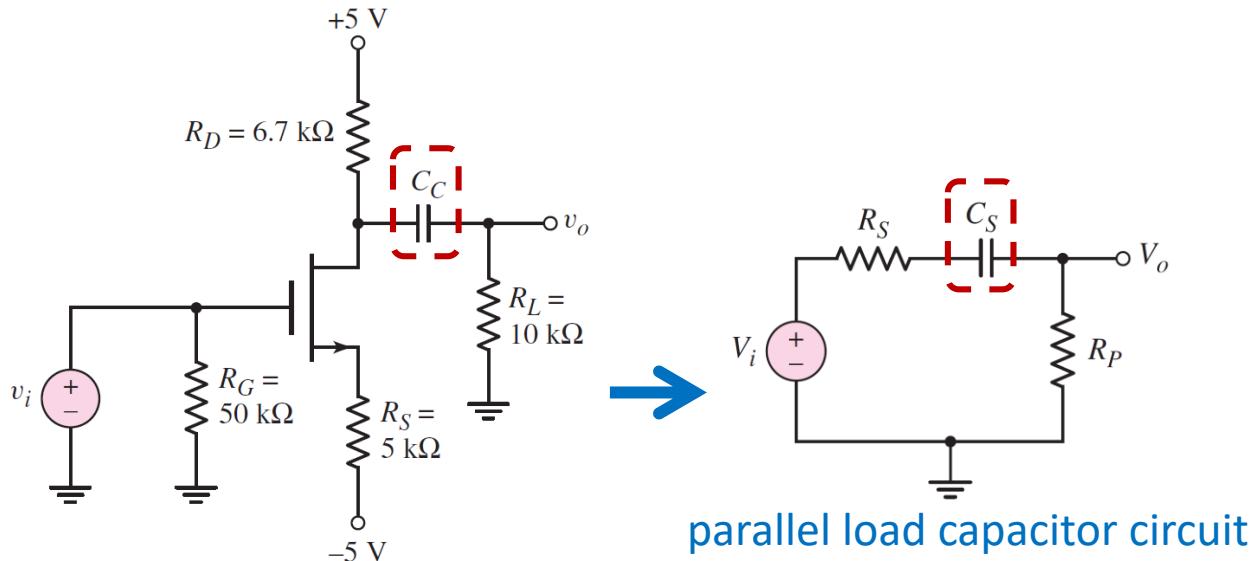
# Common-Source Circuit with Coupling Capacitor

- The output signal is connected to the load through a **coupling capacitor**
- This common-source MOSFET amplifier is equivalent to a **parallel load capacitor circuit** (RC circuit 2)



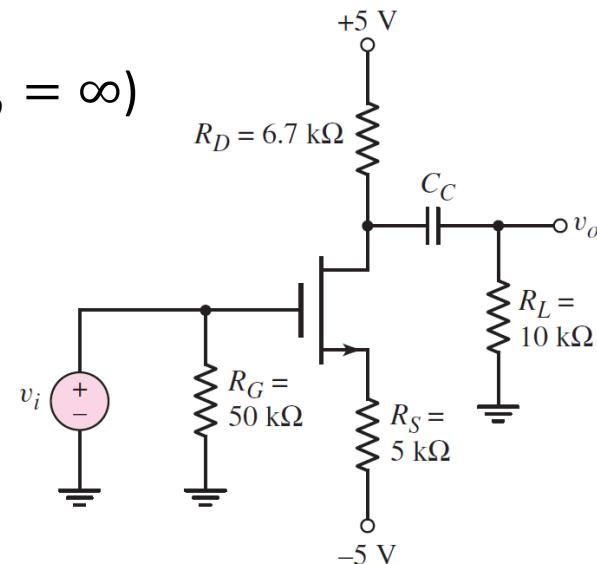
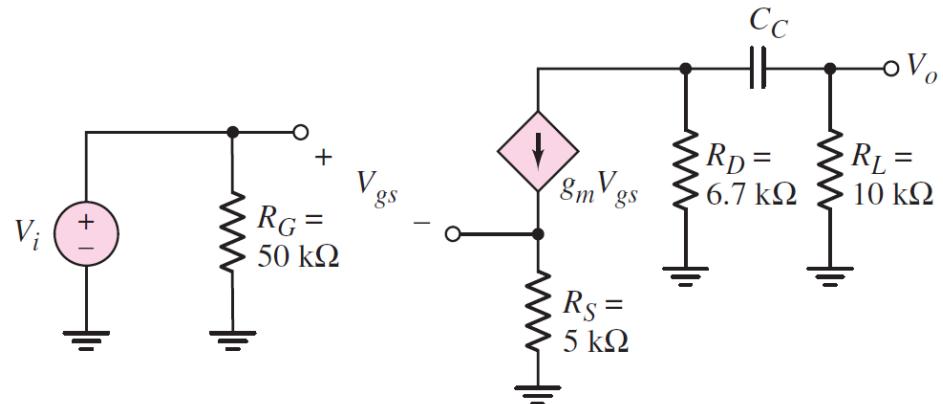
# Common-Source Circuit with Coupling Capacitor

- This circuit is a **low-pass network**
  - The **maximum small-signal voltage gain** (in dB) ← we found this value in Chapter 5
  - The lower corner frequency  $f_L$



# Common-Source Circuit with Coupling Capacitor

- To find the **maximum small-signal voltage gain**, we need to draw the small-signal equivalent circuit (step 2 ac analysis)
  - Set all dc sources to zero
  - Assume the frequency is high enough, so  $C_C$  can be treated as a short circuit
  - Replace the FET by small-signal model (assume  $r_o = \infty$ )



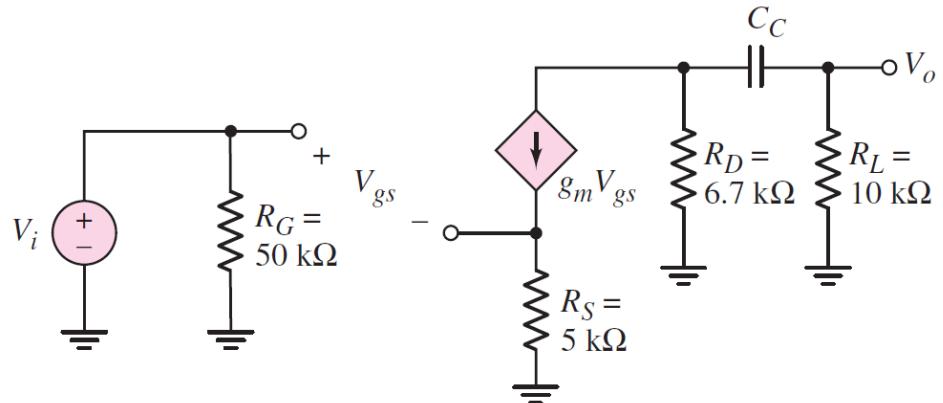
# Common-Source Circuit with Coupling Capacitor

- The output voltage is

$$V_o = -g_m V_{gs} (R_D \parallel R_L)$$

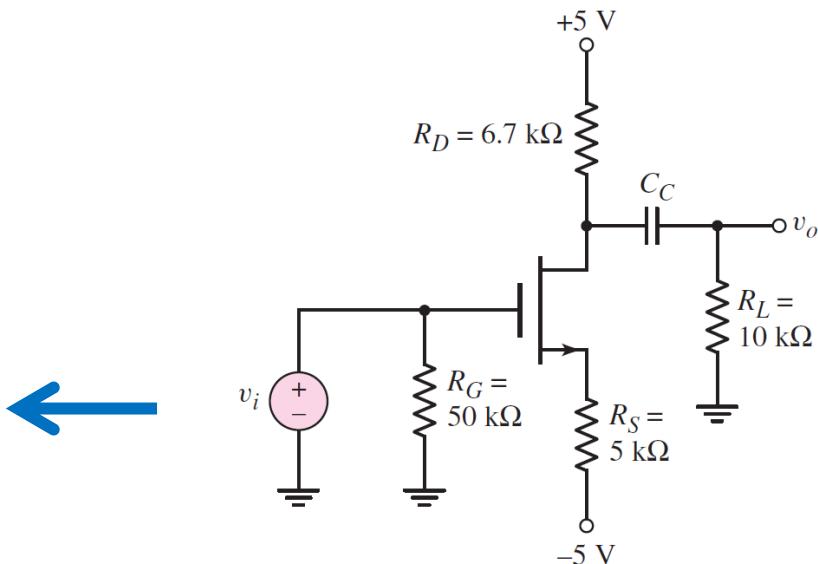
- The input voltage is

$$V_i = V_{gs} + g_m R_S V_{gs}$$



- The maximum small-signal voltage gain is

$$|A_v(\max)| = \frac{g_m (R_D \parallel R_L)}{1 + g_m R_S}$$



# Output Coupling Capacitor: Common-Source Circuit

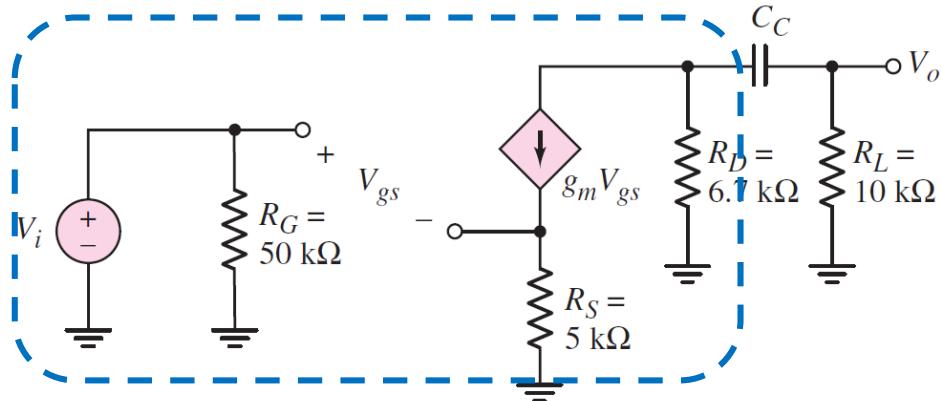
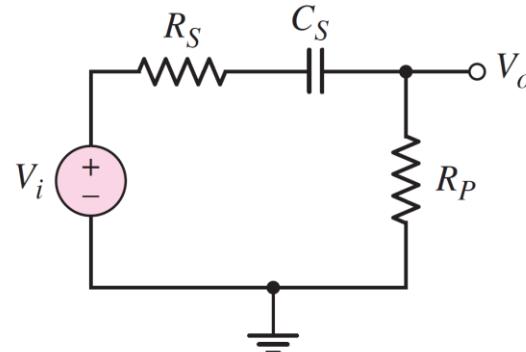
- The time constant is a function of the **effective resistance** seen by capacitor  $C_C$

- Set all independent sources equal to zero  $V_i = 0$

$$\tau_s = (R_o + R_L)C_C = (R_D + R_L)C_C$$

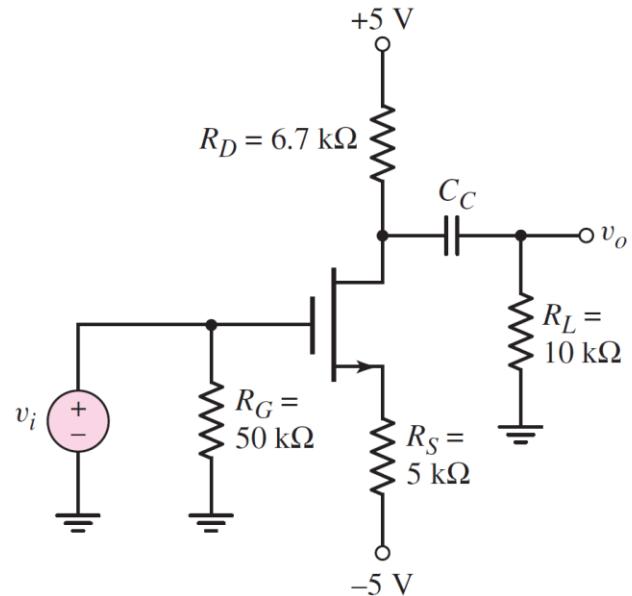
- The lower corner frequency is

$$f_L = \frac{1}{2\pi\tau_s} = \frac{1}{2\pi(R_D + R_L)C_C}$$



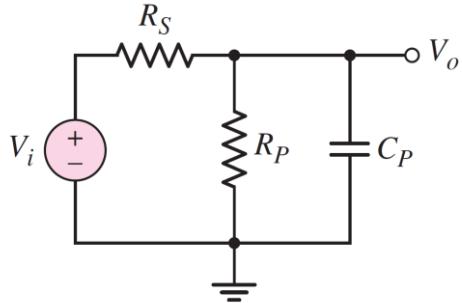
# Example 7.4

This circuit is to be used as a simple audio amplifier. Design the circuit such that the lower corner frequency is  $f_L = 20$  Hz.

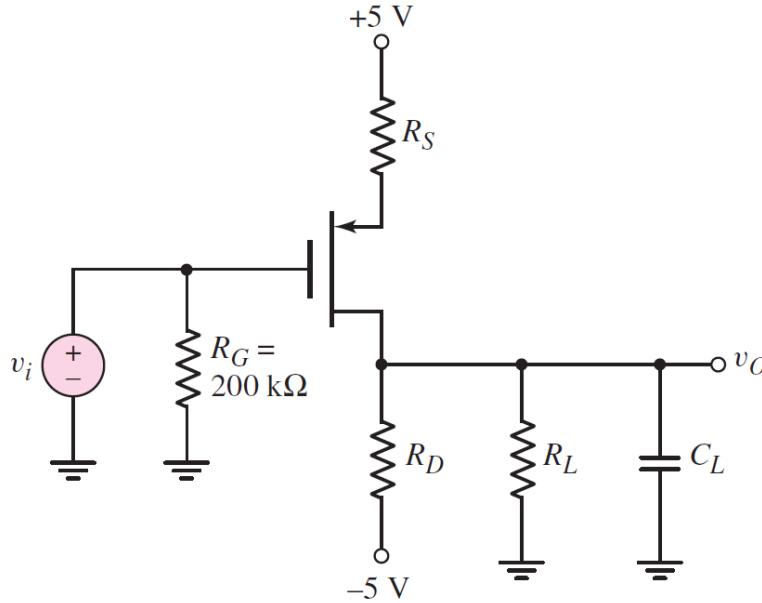


# Transistor Amplifiers with Capacitors

- Three types of capacitors will be considered
  - Coupling capacitor, **load capacitor**, and bypass capacitor
- What is the **Bode plot** of this amplifier circuit?

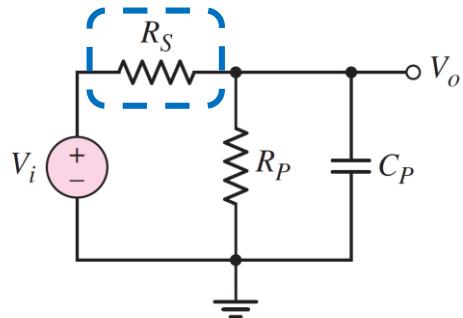


Parallel load capacitor circuit  
(low-pass network)

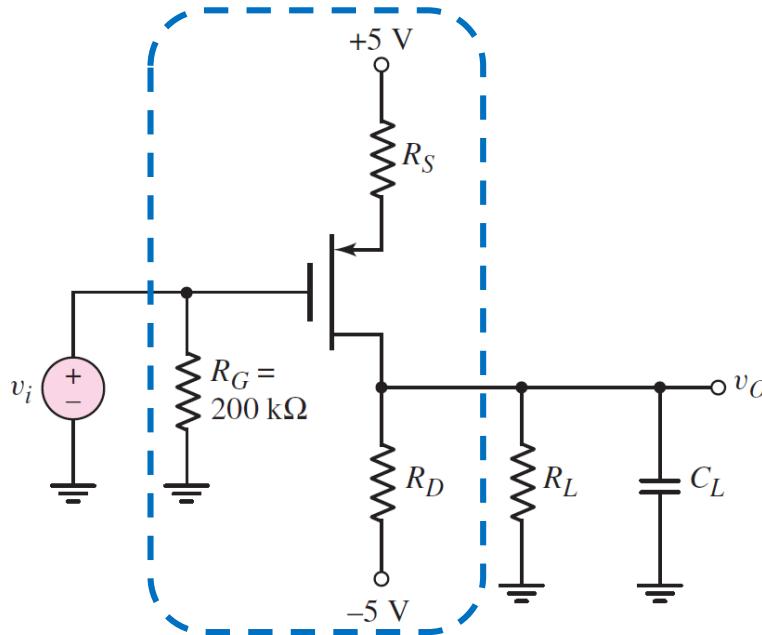


# Load Capacitor Effects

- This is a **low-pass network**
- Draw the general shape of the **Bode plot**
  - **Upper corner frequency**
  - The maximum **small-signal voltage gain**



Parallel load capacitor circuit  
(low-pass network)



# Load Capacitor Effects

- The effective resistance seen by the load capacitor is

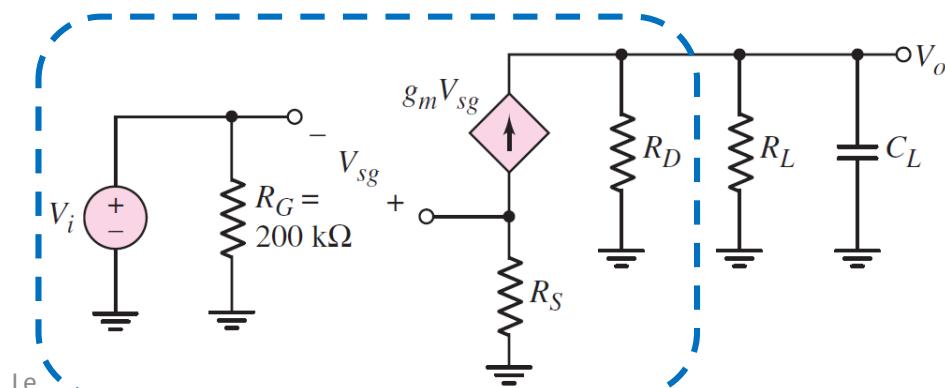
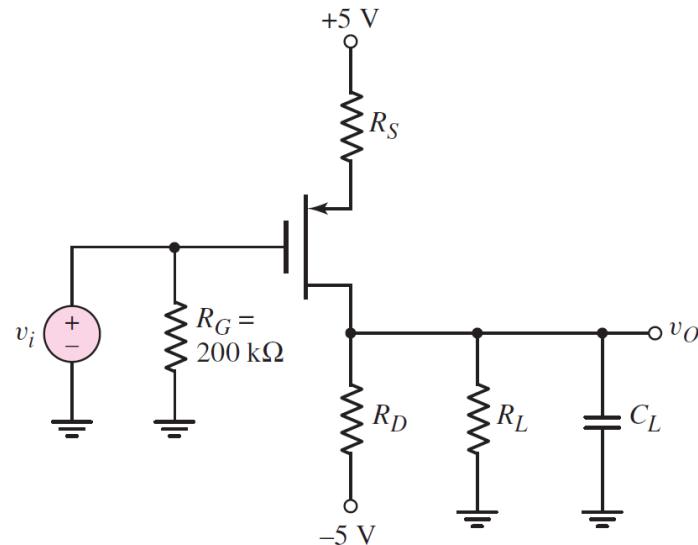
- $R_{eq} = R_o \parallel R_L$

- The time constant is

- $\tau_P = R_{eq} C_L$

- The upper corner frequency is

$$f_H = \frac{1}{2\pi\tau_P}$$



# Load Capacitor Effects

- The **maximum** small-signal voltage gain is

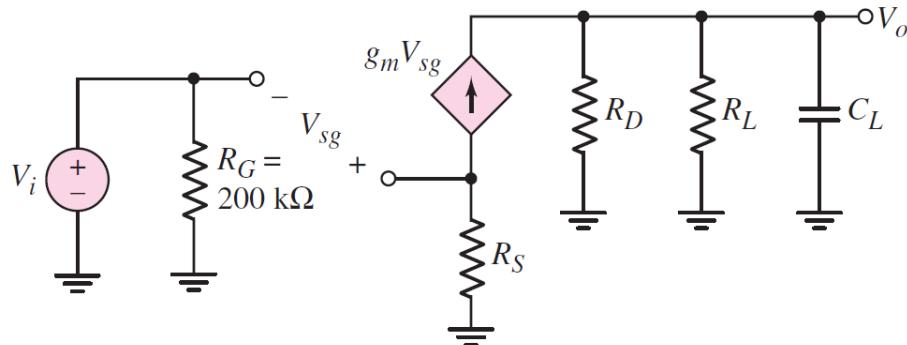
$$|A_v|_{\max} = \frac{g_m(R_D \parallel R_L)}{1 + g_m R_S}$$

- $C_L$  is treated as an **open circuit**
- The output voltage is

$$V_o = g_m V_{sg} (R_D \parallel R_L)$$

- The input voltage is

$$V_i = -(1 + g_m R_S) V_{sg}$$

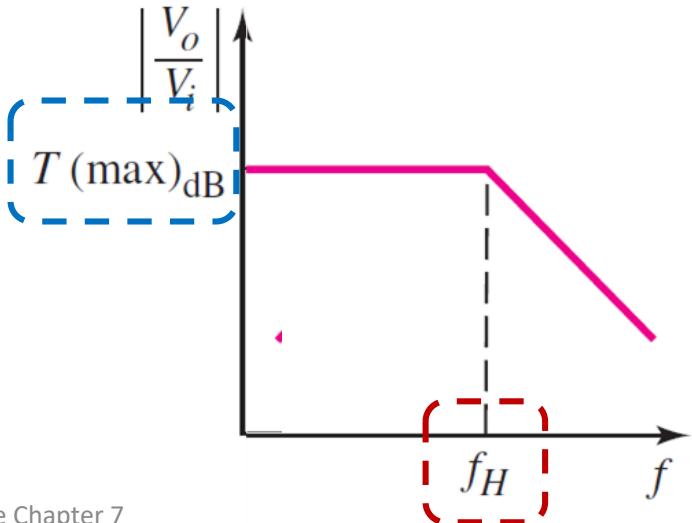
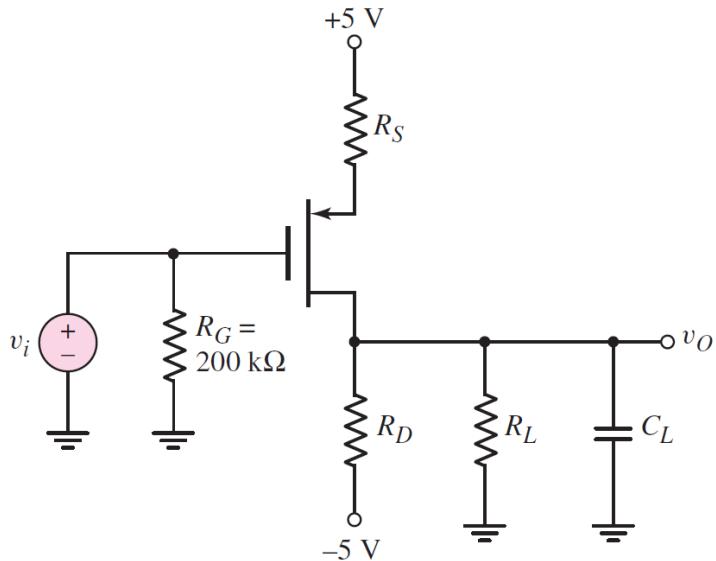


# Load Capacitor Effects

- The **Bode plot** of the common-source with source resistor circuit is

$$|A_v|_{\max} = \frac{g_m(R_D \parallel R_L)}{1 + g_m R_S}$$

$$f_H = \frac{1}{2\pi(R_o \parallel R_L)C_L}$$

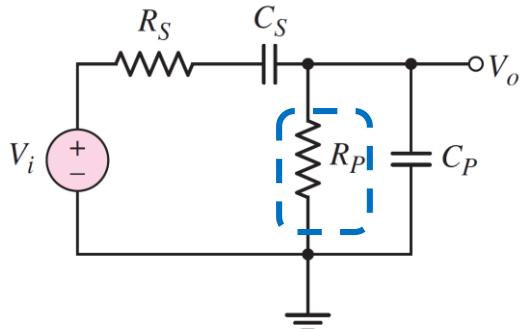


# Problem-Solving Technique: Bode Plot

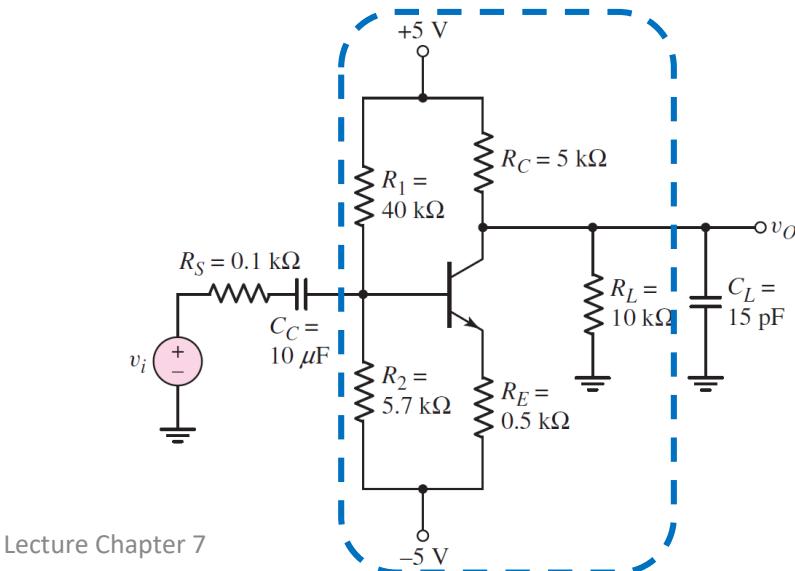
- For a particular capacitor:
  - 1. Determine whether the capacitor is producing a **low-pass** or **high-pass circuit**
    - Sketch the general shape of the **Bode plot**
  - 2. Find the corner frequency from  $f = 1/2\pi\tau$ 
    - The time constant is  $\tau = R_{eq}C$
    - The  $R_{eq}$  is the effective resistance seen by the **capacitor**
  - 3. Find **maximum gain magnitude (mid-band gain)**
    - Coupling and bypass capacitors act as **short circuits**
    - Load capacitors act as **open circuits**
    - See more details in Chapter 5 and 6

# Coupling and Load Capacitors

- A circuit with both a coupling capacitor and load capacitor
- The values of these two capacitor differ by orders of magnitude
  - $C_C \gg C_L$
- The corner frequencies are far apart and can be treated separately



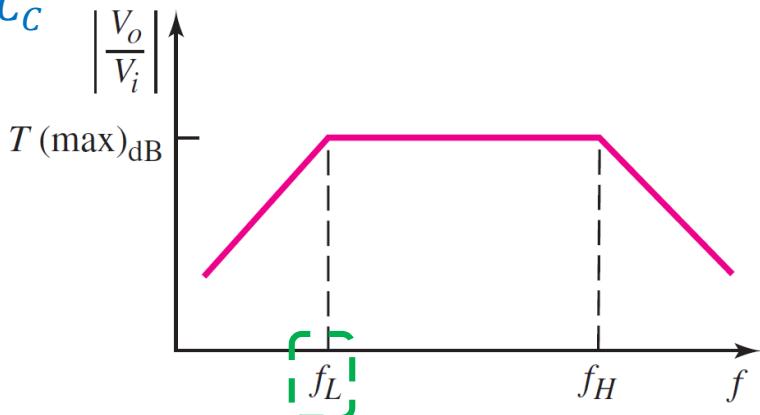
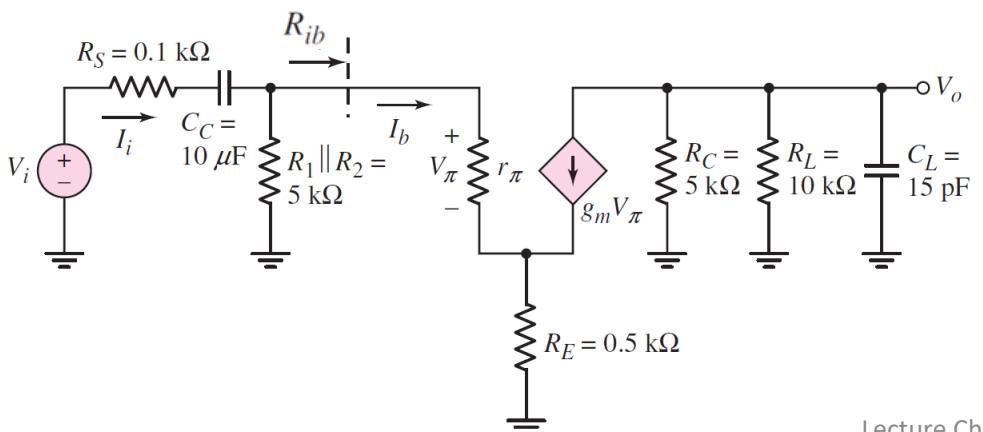
Combination of RC circuit 1 and 2



# Coupling and Load Capacitors

- The **effective resistance** seen by the coupling capacitor  $C_C$  is
  - $R_{eq} = R_S + (R_1 \parallel R_2 \parallel R_{ib})$
  - $R_{ib} = r_\pi + (1 + \beta)R_E$
- The **lower corner frequency** is

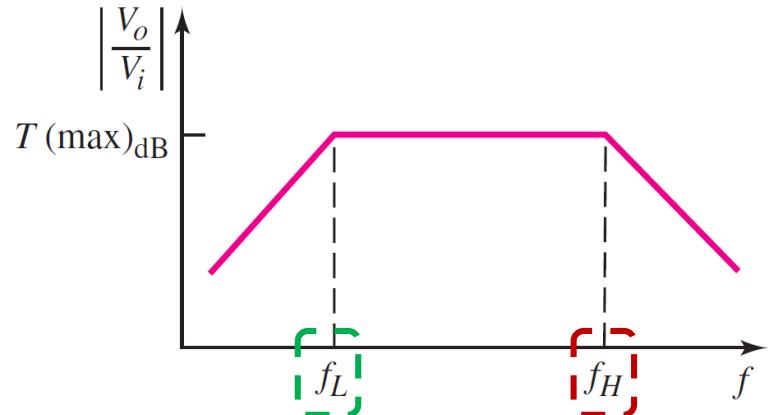
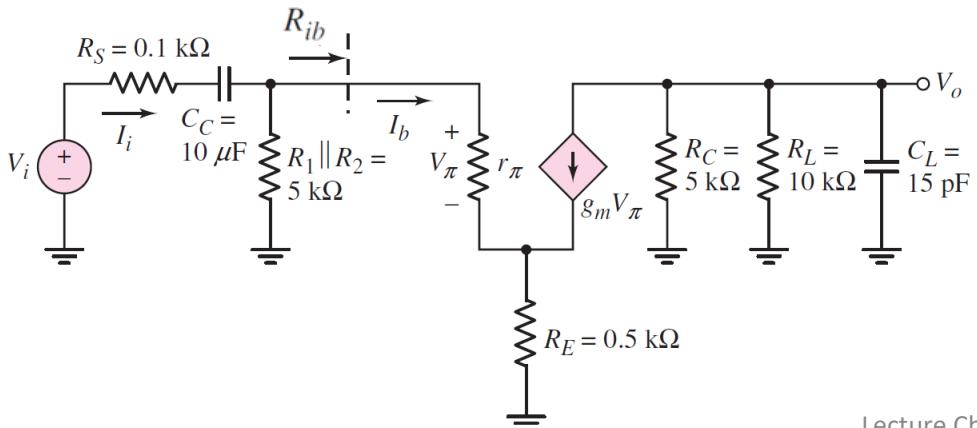
$$f_L = \frac{1}{2\pi\tau_S} = \frac{1}{2\pi R_{eq} C_C} = \frac{1}{2\pi [R_S + (R_1 \parallel R_2 \parallel R_{ib})] C_C}$$



# Coupling and Load Capacitors

- The **effective resistance** seen by the load capacitor  $C_L$  is
  - $R_{eq} = R_C \parallel R_L$
- The **upper corner frequency** is

$$f_H = \frac{1}{2\pi\tau_P} = \frac{1}{2\pi R_{eq} C_L} = \frac{1}{2\pi(R_C \parallel R_L) C_C}$$

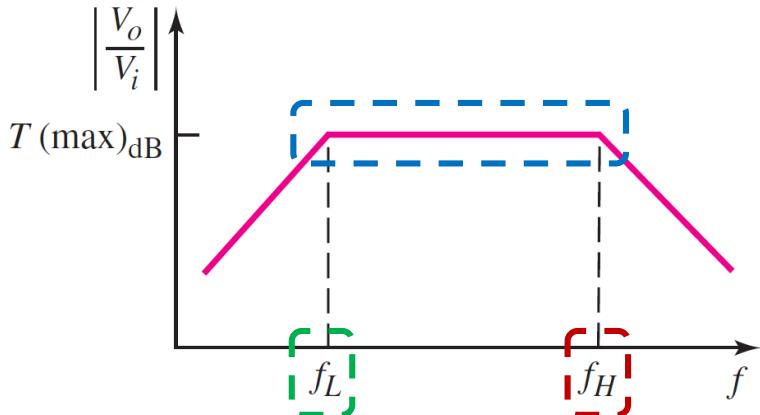
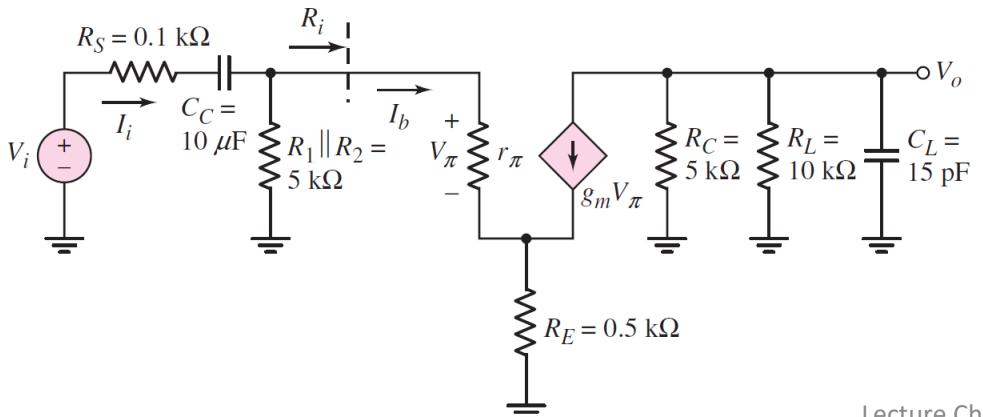


# Coupling and Load Capacitors

- The magnitude of the mid-band gain (the maximum gain) is

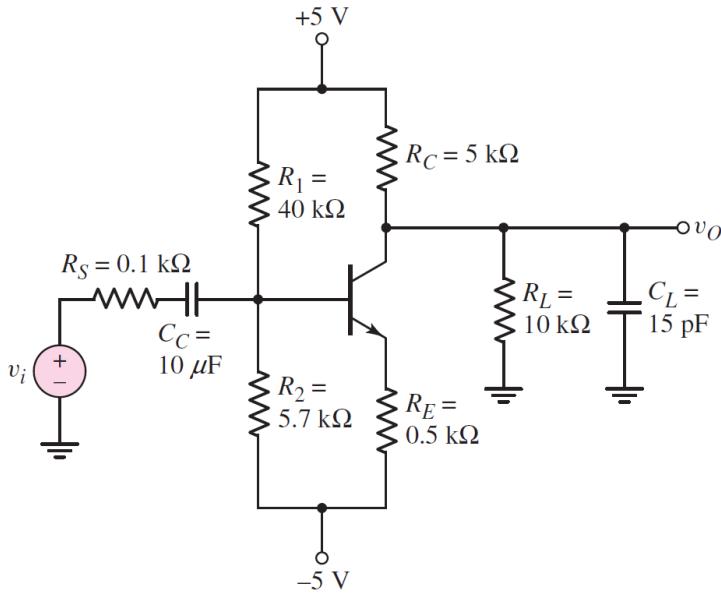
$$|A_v|_{\max} = g_m r_\pi (R_C \parallel R_L) \left( \frac{R_1 \parallel R_2}{(R_1 \parallel R_2) + R_i} \right) \left( \frac{1}{R_S + (R_1 \parallel R_2 \parallel R_i)} \right)$$

- The frequency is high enough ( $f \gg f_L$ ), so  $C_C$  acts as a short circuit
- The frequency is low enough ( $f \ll f_H$ ), so  $C_L$  acts as an open circuit



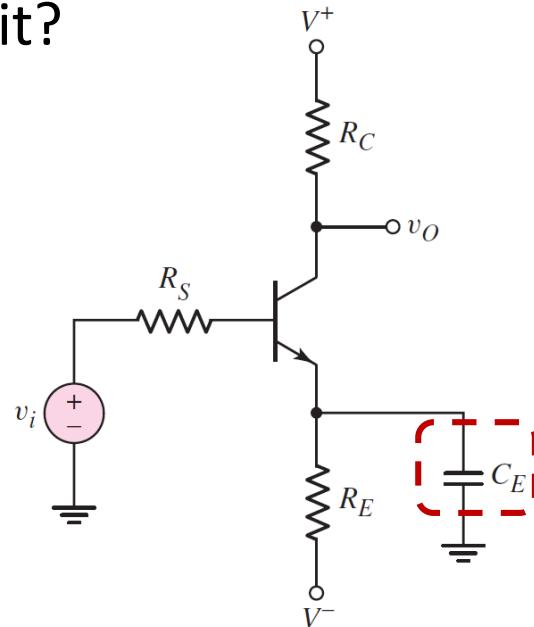
# Example 7.5

Determine the mid-band gain, corner frequencies, and bandwidth of a circuit containing both a coupling capacitor and a load capacitor. The transistor parameters are  $V_{BE}(\text{on}) = 0.7 \text{ V}$ ,  $\beta = 100$ ,  $V_A = \infty$ .



# Transistor Amplifiers with Capacitors

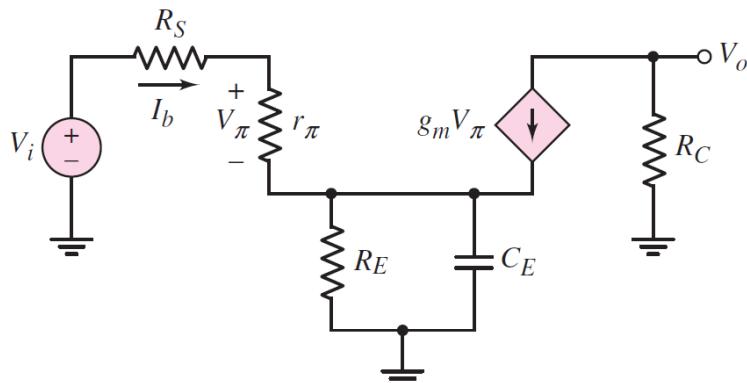
- Three types of capacitors will be considered
  - Coupling capacitor, load capacitor, and **bypass capacitor**
- This is a common-emitter circuit with an **emitter bypass capacitor**
- What is the **Bode plot** of this amplifier circuit?



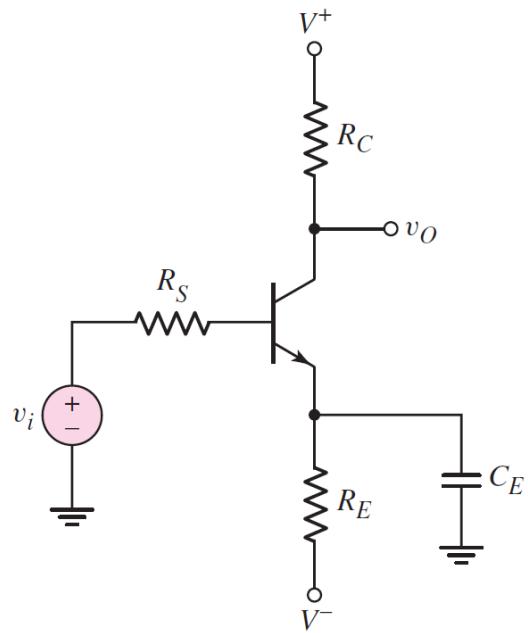
# Bypass Capacitor Effects

- Draw the **small-signal equivalent circuit**
- The output voltage is

$$V_o = -g_m V_\pi R_C = -g_m (I_b r_\pi) R_C$$



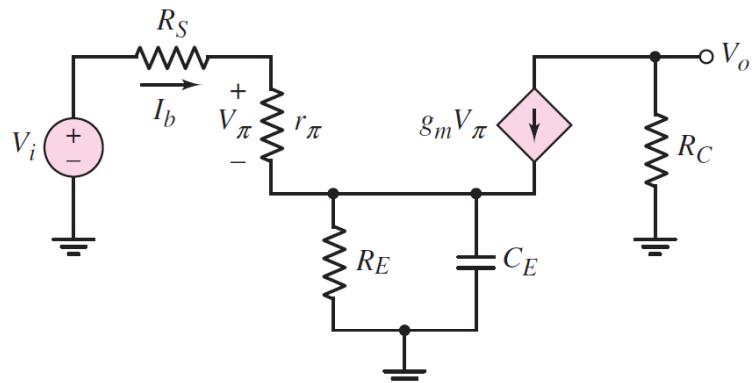
small-signal equivalent circuit



# Bypass Capacitor Effects

- The base current is the input current

$$I_b = I_b = \frac{V_i}{R_S + R_{ib}} = \frac{V_i}{R_S + \left[ r_\pi + (1 + \beta) \left( R_E \parallel \frac{1}{sC_E} \right) \right]}$$



small-signal equivalent circuit

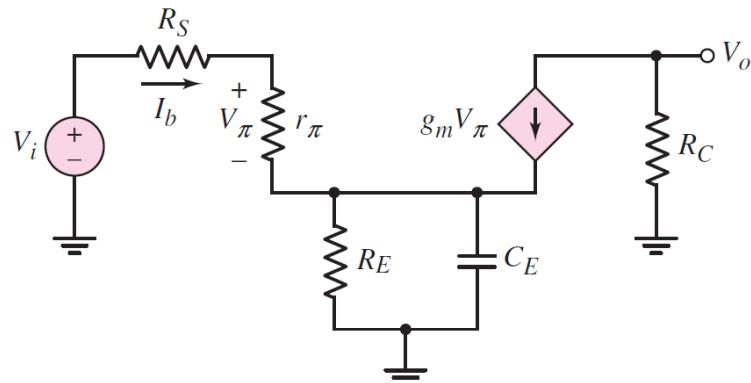
# Bypass Capacitor Effects

- Combining previous two equations, we can get

$$V_o = -g_m(I_b r_\pi) R_C = -g_m \frac{V_i}{R_S + r_\pi + (1 + \beta) \left( R_E \parallel \frac{1}{sC_E} \right)} r_\pi R_C$$

- The small-signal voltage gain is

$$A_v(s) = -\frac{g_m r_\pi R_C}{R_S + r_\pi + (1 + \beta) \left( R_E \parallel \frac{1}{sC_E} \right)}$$



# Bypass Capacitor Effects

$$A_v(s) = -\frac{g_m r_\pi R_C}{R_S + r_\pi + (1 + \beta) \left( R_E \parallel \frac{1}{sC_E} \right)}$$

- Expanding the parallel combination of  $R_E$  and  $\frac{1}{sC_E}$  rearranging terms, we find

$$A_v(s) = -\frac{g_m r_\pi R_C}{R_S + r_\pi + (1 + \beta)R_E} \times \frac{1 + sR_E C_E}{1 + s \frac{R_E(R_S + r_\pi)C_E}{R_S + r_\pi + (1 + \beta)R_E}}$$

- We can write the voltage gain in terms of time constants as

$$A_v(s) = -\frac{g_m r_\pi R_C}{R_S + r_\pi + (1 + \beta)R_E} \times \frac{1 + s\tau_A}{1 + s\tau_B}$$

$$\tau_A = R_E C_E$$

$$\tau_B = \frac{R_E(R_S + r_\pi)C_E}{R_S + r_\pi + (1 + \beta)R_E}$$

# Bypass Capacitor Effects

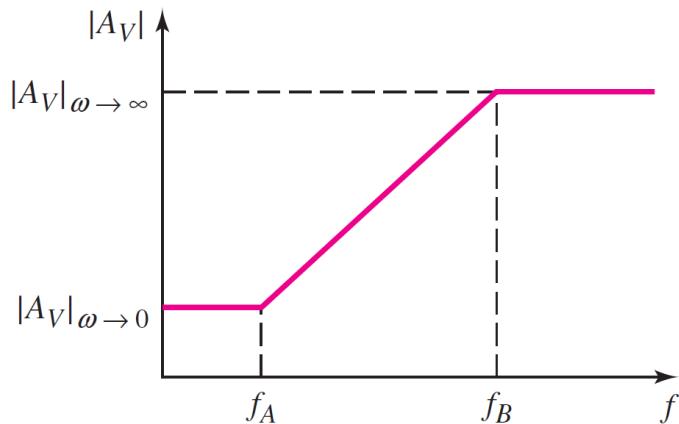
$$A_v(s) = -\frac{g_m r_\pi R_C}{R_S + r_\pi + (1 + \beta)R_E} \times \frac{1 + s\tau_A}{1 + s\tau_B}$$

$$|A_v|_{\omega \rightarrow 0} = \frac{g_m r_\pi R_C}{R_S + r_\pi + (1 + \beta)R_E}$$

$$|A_v|_{\omega \rightarrow \infty} = \frac{g_m r_\pi R_C}{R_S + r_\pi}$$

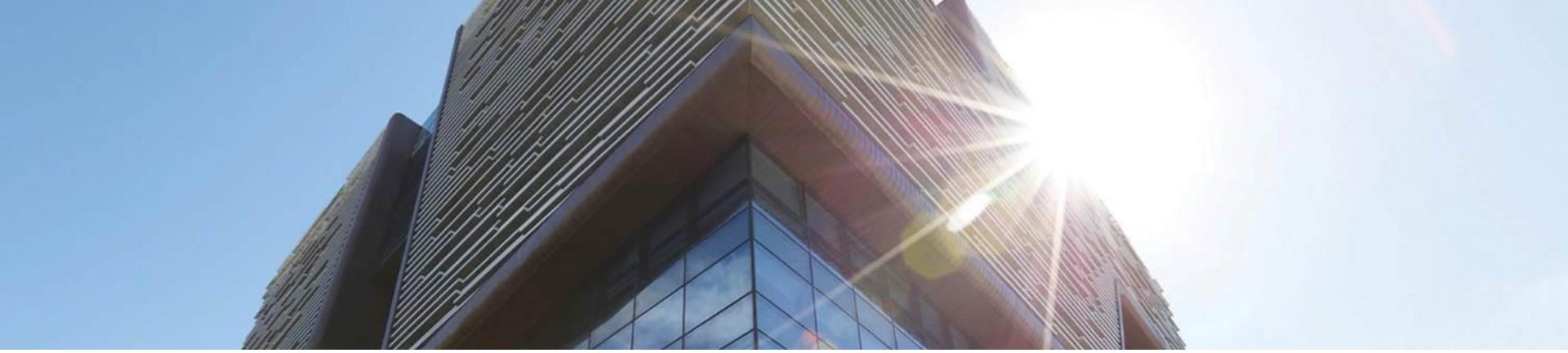
- The Bode plot of the voltage gain magnitude is

- $f_B = \frac{1}{2\pi\tau_B}$
- $f_A = \frac{1}{2\pi\tau_A}$
- $\tau_A$  and  $\tau_B$  are time constants



# Summary

- Construct the **Bode plots** of the gain magnitude from a transfer function written in terms of the complex frequency  $s$ 
  - Series coupling capacitor circuit and parallel load capacitor circuit
- Construct the **Bode plots** of the gain magnitude of amplifier circuits, taking into account circuit capacitors
  - Coupling capacitor, load capacitor and bypass capacitor
- Optional: Determine the Miller capacitance of a BJT circuit using the expanded hybrid- $\pi$  equivalent circuit
- Optional: Determine the Miller capacitance of an FET circuit using the expanded small-signal equivalent circuit
- Optional: Describe the relative frequency responses of amplifier circuits



# Thank You



# Optional: Time Response

$$T(s) = \frac{V_o(s)}{V_i(s)} = \left( \frac{R_P}{R_S + R_P} \right) \left[ \frac{s(R_S + R_P)C_S}{1 + s(R_S + R_P)C_S} \right] = K \left( \frac{s\tau_S}{1 + s\tau_S} \right)$$

- If the input voltage is a step function

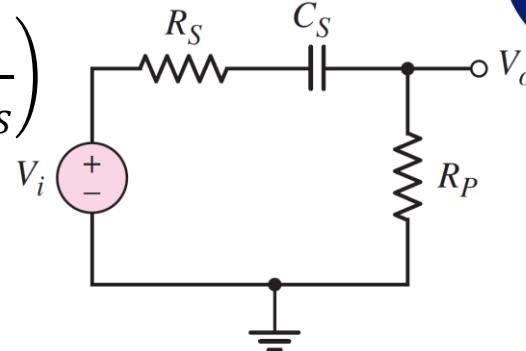
- $V_i(s) = \frac{1}{s}$

- The output voltage is

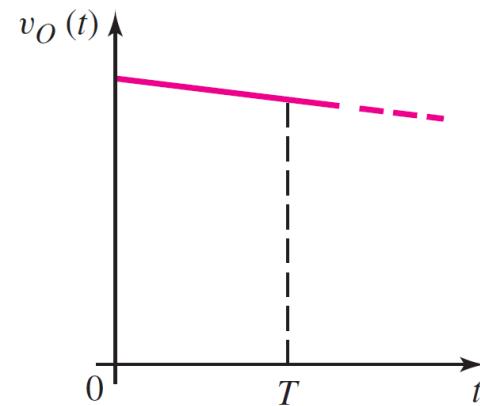
$$V_o(s) = T(s)V_i(s) = K \left( \frac{\tau_S}{1 + s\tau_S} \right) = K \left( \frac{1}{s + \frac{1}{\tau_S}} \right)$$

- Taking the inverse Laplace transform

$$v_o(t) = Ke^{-\frac{t}{\tau_S}}$$



Series coupling capacitor circuit



# Optional: Time Response

$$T(s) = \frac{V_o(s)}{V_i(s)} = \left( \frac{R_P}{R_S + R_P} \right) \left[ \frac{1}{1 + s(R_S \parallel R_P)C_P} \right] = K \left( \frac{1}{1 + s\tau_P} \right)$$

- If the input voltage is a step function

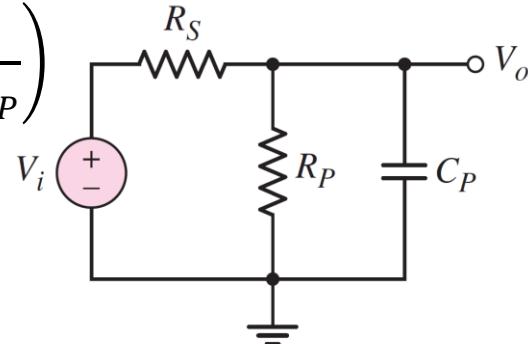
- $V_i(s) = \frac{1}{s}$

- The output voltage is

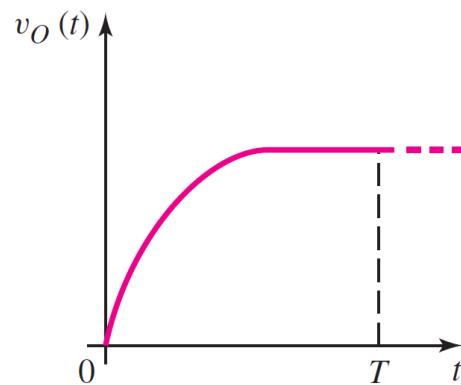
$$V_o(s) = T(s)V_i(s) = \frac{K}{s} \left( \frac{1}{1 + s\tau_P} \right) = \frac{K}{s} \left( \frac{1/\tau_P}{s + 1/\tau_P} \right)$$

- Taking the inverse Laplace transform

$$v_o(t) = K \left( 1 - e^{-\frac{t}{\tau_P}} \right)$$



Parallel load capacitor circuit



# Frequency Response: Bipolar Transistor (Optional)

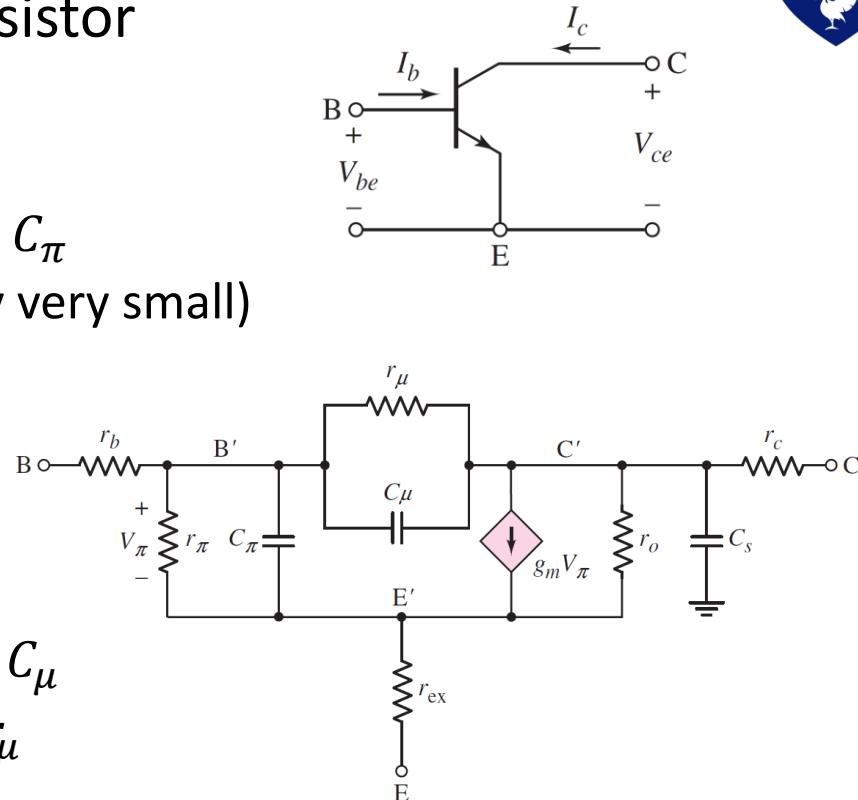
Determine the frequency response of the bipolar transistor, and determine the Miller effect and Miller capacitance.

# Frequency Response: Bipolar Transistor

- The frequency response of circuits as a function of **external resistors and capacitors**, and we have assumed the transistor to be ideal.
- However, both bipolar transistors and FETs have **internal capacitances** that influence the high-frequency response of circuits.
- Develop an **expanded small-signal hybrid- $\pi$  model** of the bipolar transistor
- Analyze the frequency characteristics of the bipolar transistor.

# Expanded Small-Signal Hybrid- $\pi$ Model

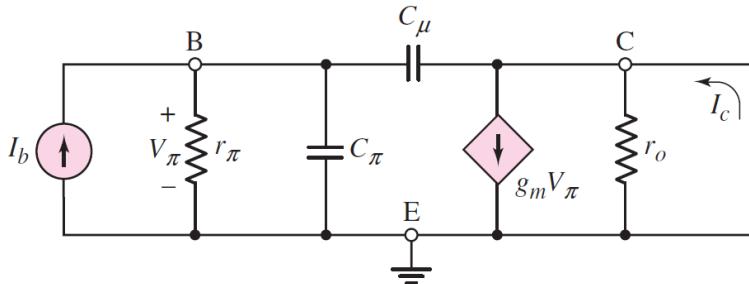
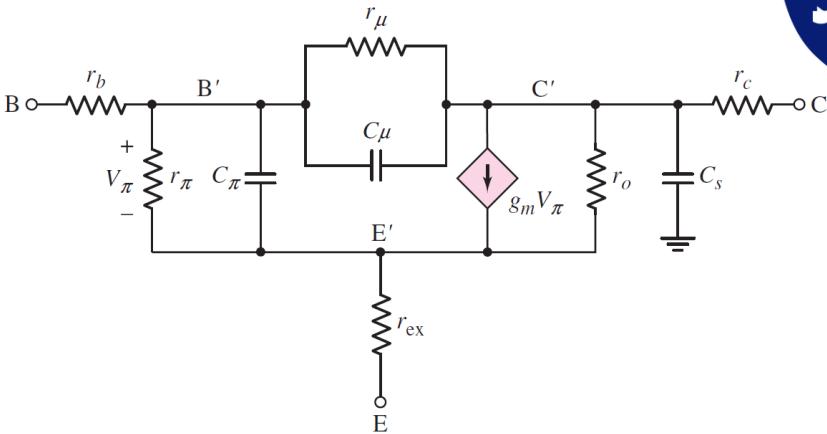
- Common-emitter npn bipolar transistor
- Base to emitter
  - Base series resistance  $r_b$
  - Forward biased junction capacitance  $C_\pi$
  - Emitter series resistance  $r_{ex}$  (usually very small)
- Collector to emitter
  - Collector series resistance  $r_c$
  - Junction capacitance  $C_s$
- Base to collector
  - Reverse-biased junction capacitance  $C_\mu$
  - Reverse-biased diffusion resistance  $r_\mu$



# Short-Circuit Current Gain

- Simplified hybrid- $\pi$  equivalent circuit
  - $r_b$ ,  $r_c$ ,  $r_{ex}$ ,  $r_\mu$ , and  $C_s$  are neglected
  - The transistor must still be biased in the **forward-active region**
- Writing KCL equation

$$I_b = \frac{V_\pi}{r_\pi} + \frac{V_\pi}{\frac{1}{j\omega C_\pi}} + \frac{V_\pi}{\frac{1}{j\omega C_\mu}}$$



# Short-Circuit Current Gain

- Writing KCL equation at the output node

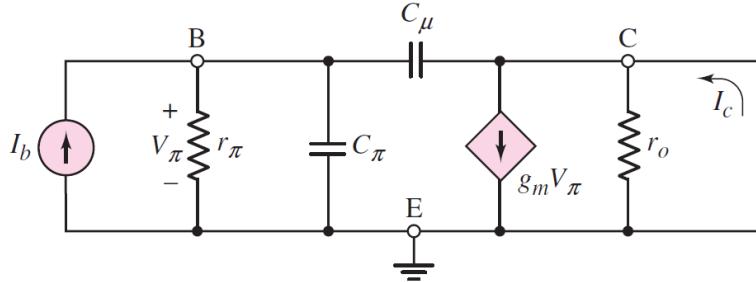
$$\frac{V_\pi}{\frac{1}{j\omega C_\mu}} + I_c = g_m V_\pi$$

$$I_c = V_\pi(g_m - j\omega C_\mu)$$

$$I_b = \frac{I_c}{(g_m - j\omega C_\mu)} \left[ \frac{1}{r_\pi} + j\omega(C_\pi + C_\mu) \right]$$

- The small-signal current gain is

$$A_i = \frac{I_c}{I_b} = h_{fe} = \frac{g_m - j\omega C_\mu}{\frac{1}{r_\pi} + j\omega(C_\pi + C_\mu)} \cong \frac{g_m r_\pi}{1 + j\omega r_\pi(C_\pi + C_\mu)}$$



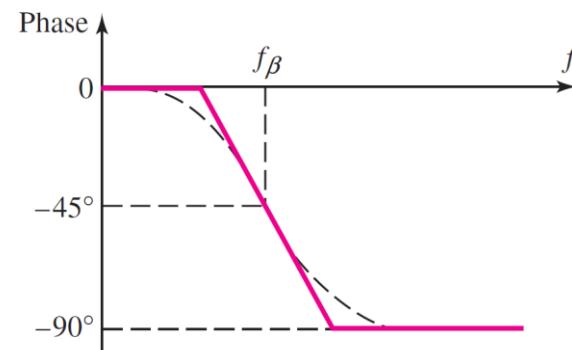
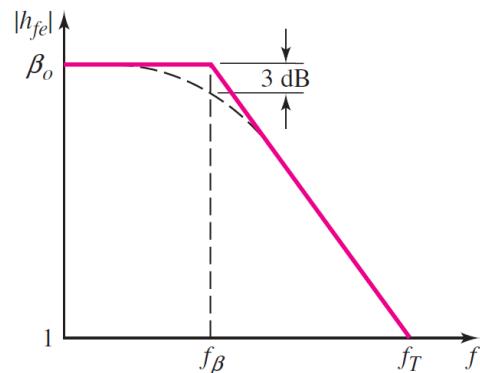
# Short-Circuit Current Gain

- The low frequency current gain is just  $\beta$

$$h_{fe} \cong \frac{g_m r_\pi}{1 + j\omega r_\pi(C_\pi + C_\mu)} = \frac{\beta}{1 + j\omega r_\pi(C_\pi + C_\mu)}$$

- Beta cutoff frequency (corner frequency) is

$$f_\beta = \frac{1}{2\pi r_\pi(C_\pi + C_\mu)}$$



# Cutoff Frequency

- At the **cutoff frequency**  $f_T$ , the gain goes to 1

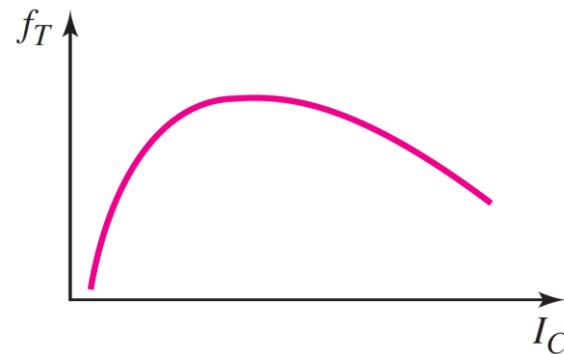
$$h_{fe} = \frac{\beta}{1 + j\omega r_\pi(C_\pi + C_\mu)} = \frac{\beta}{1 + j\left(\frac{f}{f_\beta}\right)}$$

$$1 = \frac{\beta}{\sqrt{1 + \left(\frac{f_T}{f_\beta}\right)^2}} \cong \frac{\beta}{\sqrt{\left(\frac{f_T}{f_\beta}\right)^2}} = \frac{\beta f_\beta}{f_T}$$

- Unity-gain bandwidth**

$$f_T = \beta f_\beta = \beta \frac{1}{2\pi r_\pi(C_\pi + C_\mu)} = \frac{g_m}{2\pi(C_\pi + C_\mu)}$$

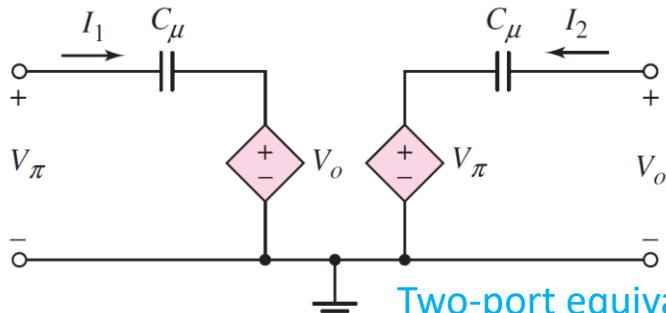
- The cutoff frequency is also a function of the dc collector current  $I_C$



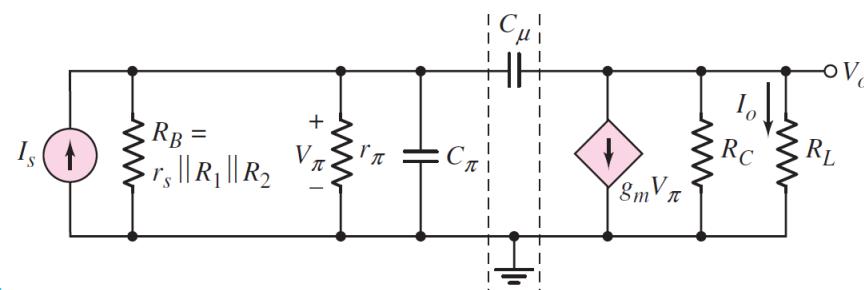
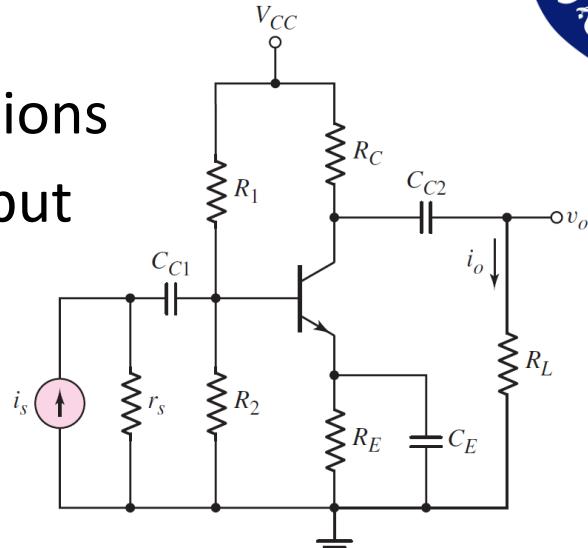
# Miller Effect and Miller Capacitance

- The **Miller effect**, or feedback effect, is a multiplication effect of  $C_\mu$  in circuit applications
- Writing KVL equations at the input and output terminals

$$V_\pi = I_1 \left( \frac{1}{j\omega C_\mu} \right) + V_o \quad V_o = I_2 \left( \frac{1}{j\omega C_\mu} \right) + V_\pi$$

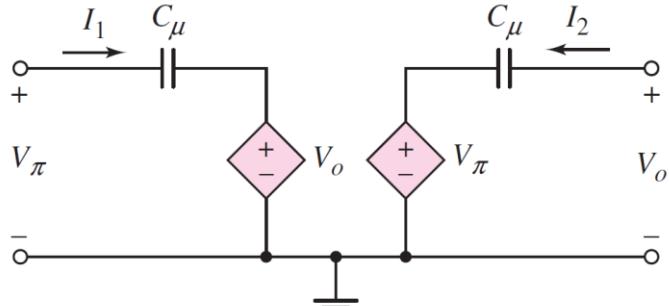


Two-port equivalent circuit of  $C_\mu$

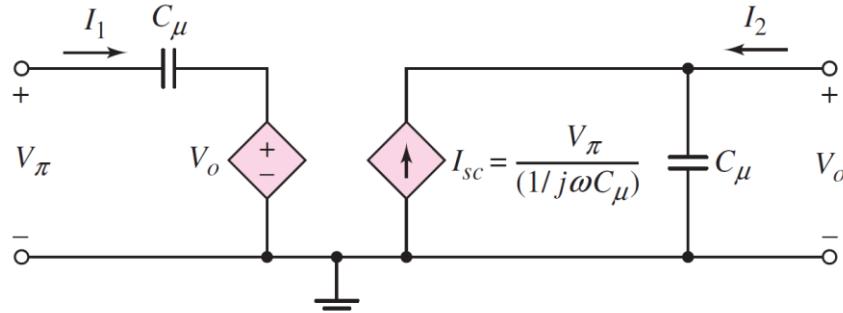


# Miller Effect and Miller Capacitance

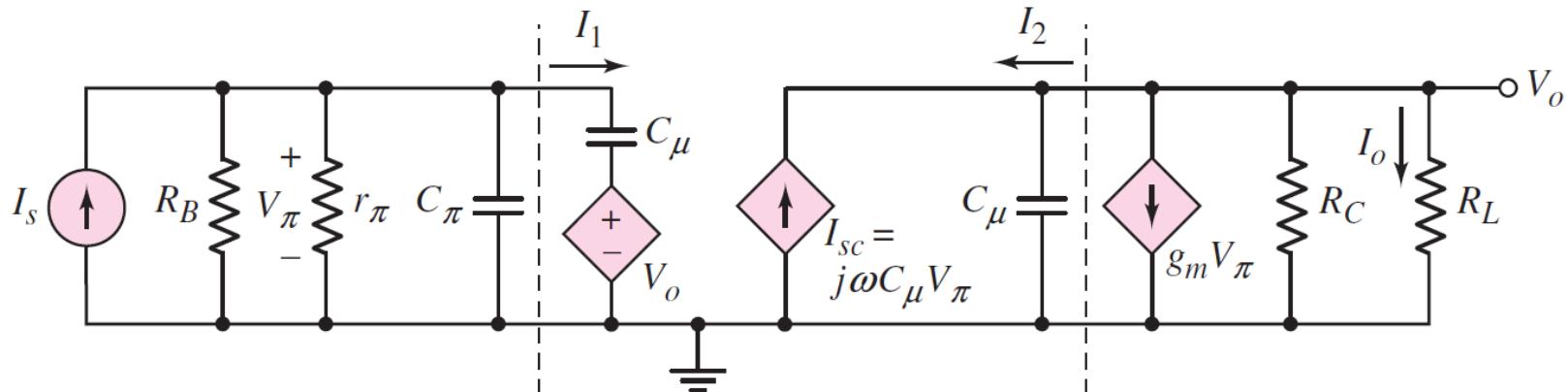
- Convert the **Thevenin** equivalent circuit to a **Norton** equivalent circuit



Thevenin equivalent circuit

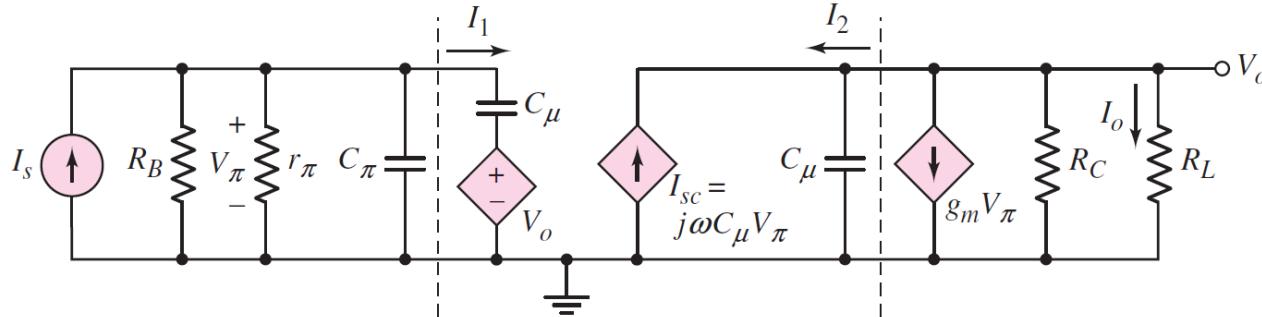


Norton equivalent circuit

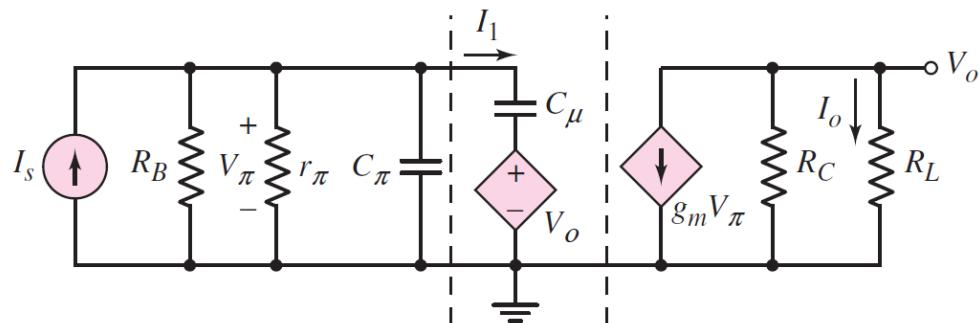


# Miller Effect and Miller Capacitance

- Usually the impedance of  $C_\mu$  is much greater than  $R_C \parallel R_L$
- $I_{SC}$  is negligible compared to the  $g_m V_\pi$  source



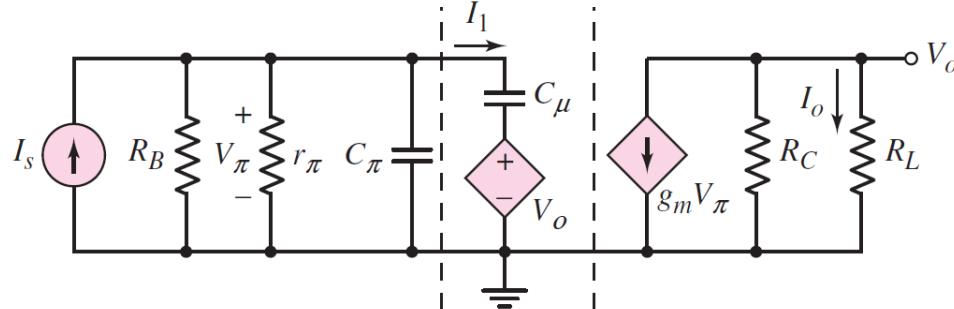
$$I_1 = \frac{V_\pi - V_o}{\frac{1}{j\omega C_\mu}} = j\omega C_\mu (V_\pi - V_o)$$



# Miller Effect and Miller Capacitance

- The output voltage is

$$V_o = -g_m V_\pi (R_C \parallel R_L)$$

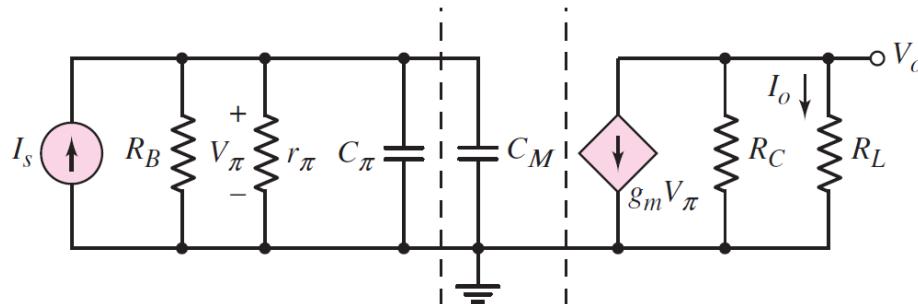


$$I_1 = j\omega C_\mu (V_\pi - V_o) = j\omega C_\mu [1 + g_m (R_C \parallel R_L)] V_\pi = j\omega C_M V_\pi$$

- $C_M$  is the **Miller capacitance**

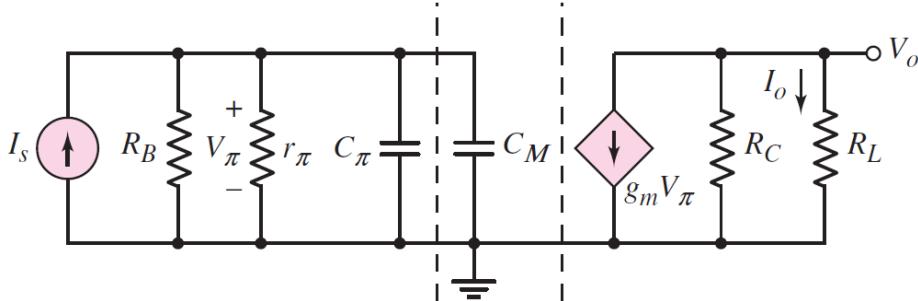
$$C_M = C_\mu [1 + g_m (R_C \parallel R_L)]$$

- The multiplication effect of  $C_\mu$  is the **Miller effect**



# Example 7.6

Determine the 3 dB frequency of the current gain for the circuit with Miller effect. The circuit parameters are  $R_C = R_L = 4 \text{ k}\Omega$ ,  $r_\pi = 2.6 \text{ k}\Omega$ ,  $R_B = 200 \text{ k}\Omega$ ,  $C_\pi = 0.8 \text{ pF}$ ,  $C_\mu = 0.05 \text{ pF}$ , and  $g_m = 38.5 \text{ mA/V}$

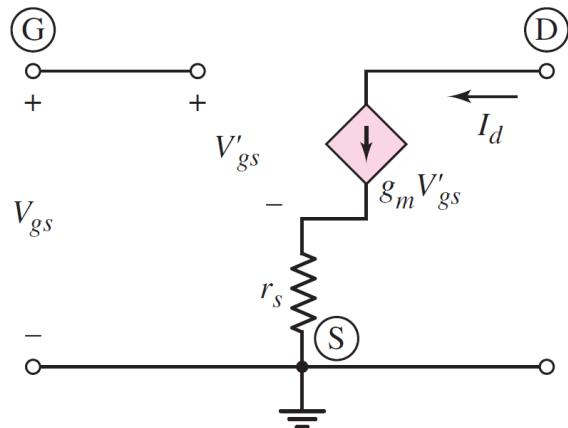


# Frequency Response: The FET (Optional)

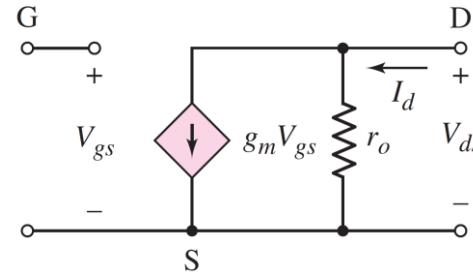
Determine the frequency response of the MOS transistor, and determine the Miller effect and Miller capacitance.

# High-Frequency Equivalent Circuit

- $V'_{gs}$  is the internal gate-source voltage
- A simplified low-frequency equivalent circuit



Simplified low-frequency equivalent circuit



Equivalent circuit of the n-channel common-source MOSFET

# Simplified Low-Frequency Equivalent Circuit

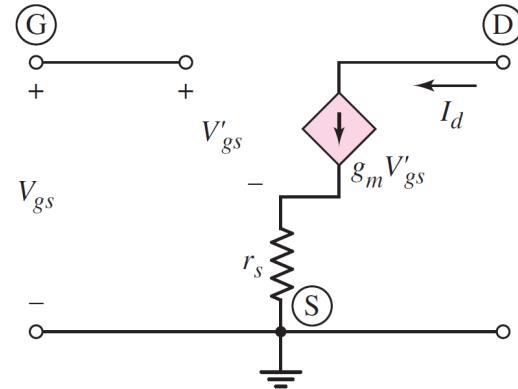
- For this circuit, the drain current is

$$I_d = g_m V'_{gs}$$

$$V_{gs} = V'_{gs} + (g_m V'_{gs}) r_s = (1 + g_m r_s) V'_{gs}$$

$$I_d = \left( \frac{g_m}{1 + g_m r_s} \right) V_{gs} = g'_m V_{gs}$$

- The p-channel MOSET is exactly the same as that of an n-channel devices
  - All voltage polarities and current directions are **reversed**



Simplified low-frequency equivalent circuit of the n-channel common-source MOSFET

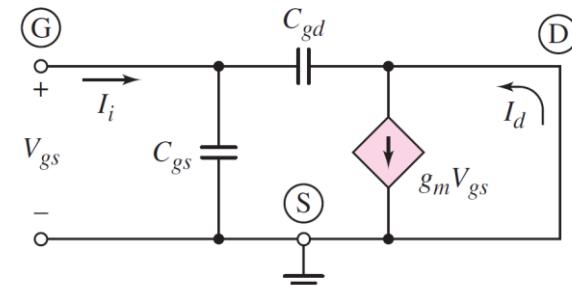
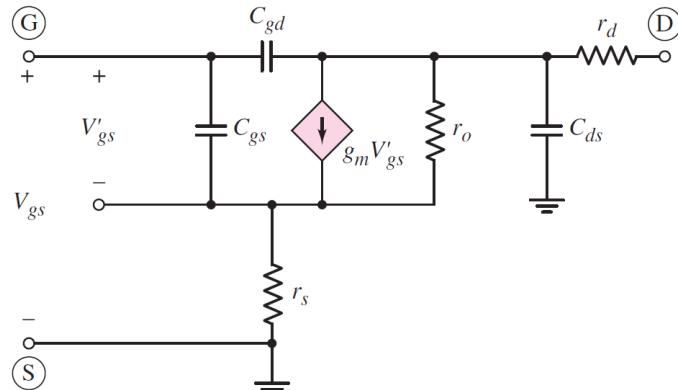
# Short-Circuit Current Gain

- Neglect  $r_s, r_d, r_o$  and  $C_{ds}$
- Short-circuit current gain
- Apply KCL equation

$$I_i = \frac{V_{gs}}{\frac{1}{j\omega C_{gs}}} + \frac{V_{gs}}{\frac{1}{j\omega C_{gd}}} = j\omega(C_{gs} + C_{gd})V_{gs}$$

$$\frac{V_{gs}}{\frac{1}{j\omega C_{gd}}} + I_d = g_m V_{gs} \quad I_d = V_{gs}(g_m - j\omega C_{gd})$$

$$A_i = \frac{I_d}{I_i} = \frac{g_m - j\omega C_{gd}}{j\omega(C_{gs} + C_{gd})} \cong \frac{g_m}{j\omega(C_{gs} + C_{gd})}$$

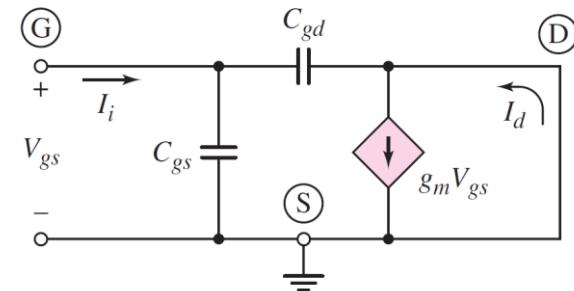


# Unity-Gain Frequency

- The **unity-gain frequency**  $f_T$  is defined as the frequency at which the magnitude of the short-circuit current gain goes to 1.

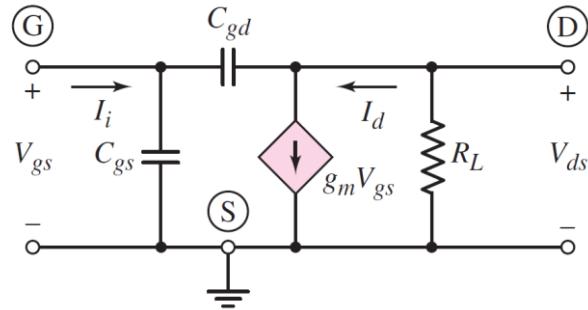
$$A_i \cong \frac{g_m}{j\omega(C_{gs} + C_{gd})} = 1$$

$$f_T = \frac{g_m}{2\pi(C_{gs} + C_{gd})}$$



# Miller Effect and Miller Capacitance

- Miller effect and Miller capacitances are factors under **high frequency**
- Find the Miller capacitance
- Writing a KCL equation



$$I_i = \frac{V_{gs}}{\frac{1}{j\omega C_{gs}}} + \frac{V_{gs} - V_{ds}}{\frac{1}{j\omega C_{gd}}} = j\omega C_{gs} V_{gs} + j\omega C_{gd} (V_{gs} - V_{ds})$$

$$\frac{V_{gs} - V_{ds}}{\frac{1}{j\omega C_{gd}}} = g_m V_{gs} + \frac{V_{ds}}{R_L}$$

$$\frac{V_{ds}}{R_L} + g_m V_{gs} + j\omega C_{gd} (V_{ds} - V_{gs}) = 0$$

# Miller Effect and Miller Capacitance

$$I_i = j\omega C_{gs}V_{gs} + j\omega C_{gd}(V_{gs} - V_{ds})$$

$$\frac{V_{ds}}{R_L} + g_m V_{gs} + j\omega C_{gd}(V_{ds} - V_{gs}) = 0$$

$$\frac{V_{ds}}{R_L} + g_m V_{gs} + j\omega C_{gd}(V_{ds} - V_{gs}) = 0$$

- Combine two equations to eliminate  $V_{ds}$

$$I_i = j\omega \left[ C_{gs} + C_{gd} \left( \frac{1 + g_m R_L}{1 + j\omega R_L C_{gd}} \right) \right] V_{gs} \cong j\omega [C_{gs} + C_{gd}(1 + g_m R_L)] V_{gs}$$

- Normally,  $\omega R_L C_{gd}$  is much less than 1

# Miller Effect and Miller Capacitance

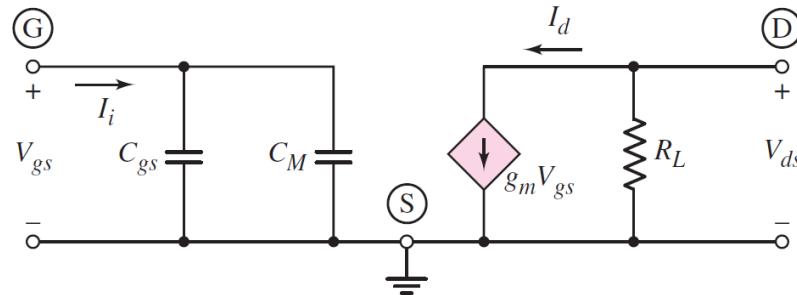
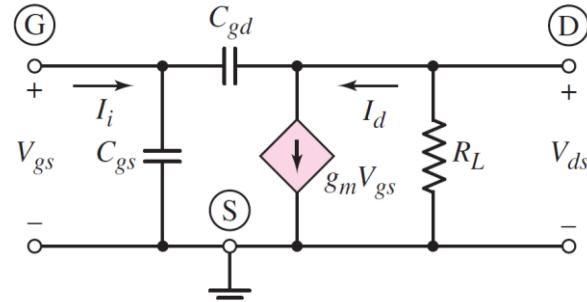
$$I_i \cong j\omega [C_{gs} + C_{gd}(1 + g_m R_L)] V_{gs} = j\omega (C_{gs} + C_M) V_{gs}$$

- $C_M$  is the **Miller capacitance**

$$C_M = C_{gd}(1 + g_m R_L)$$

- $C_G$  is the **equivalent input gate capacitance**

$$C_G = C_{gs} + C_M$$



# High Frequency Response of Transistor Circuits

Determine the high-frequency response of basic transistor circuit configurations including the cascode circuit.

# High Frequency Response of Transistor Circuits

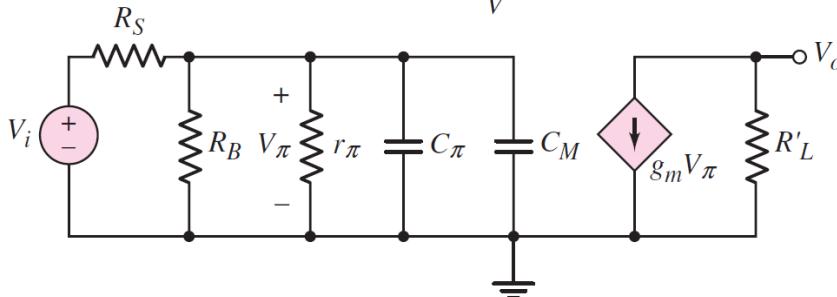
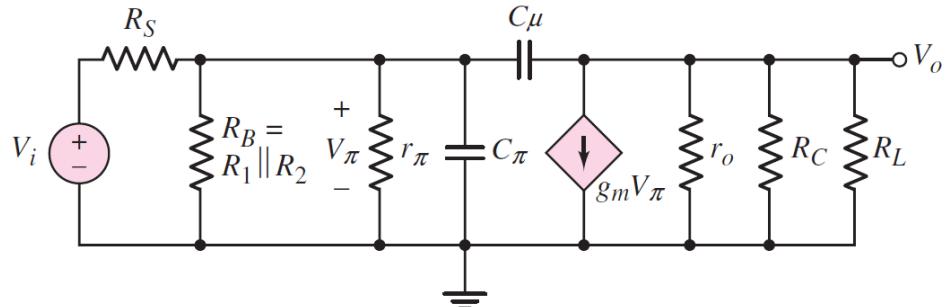
- The high-frequency equivalent circuits for **BJT** and **FET**
  - Miller effect of BJT:  $C_M = C_\mu [1 + g_m (R_C \parallel R_L)]$
  - Miller effect of FET:  $C_M = C_{gd} (1 + g_m R_L)$
- Analysis the high-frequency characteristics of transistor circuits
  - Common-emitter configuration
  - Common-source configuration

# Common-Emitter Circuit

- Assume  $C_{C1}$  and  $C_E$  are short circuits and  $C_L$  is an open circuit
- Considering the Miller effect

$$C_M = C_\mu (1 + g_m R'_L)$$

$$R'_L = r_o \parallel R_C \parallel R_L$$



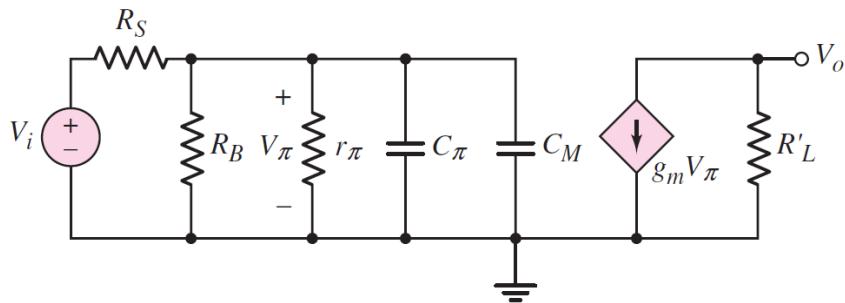
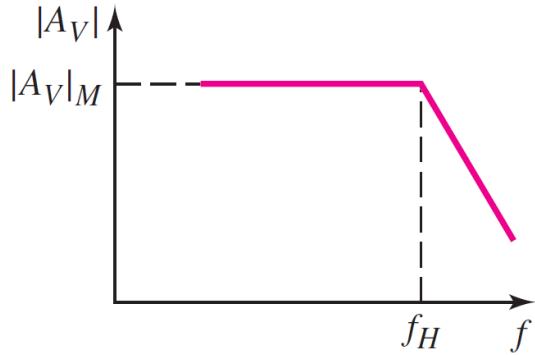
# Common-Emitter Circuit

- The upper 3 dB frequency is

$$f_H = \frac{1}{2\pi\tau_P} = \frac{1}{2\pi(R_{eq}C_{eq})}$$

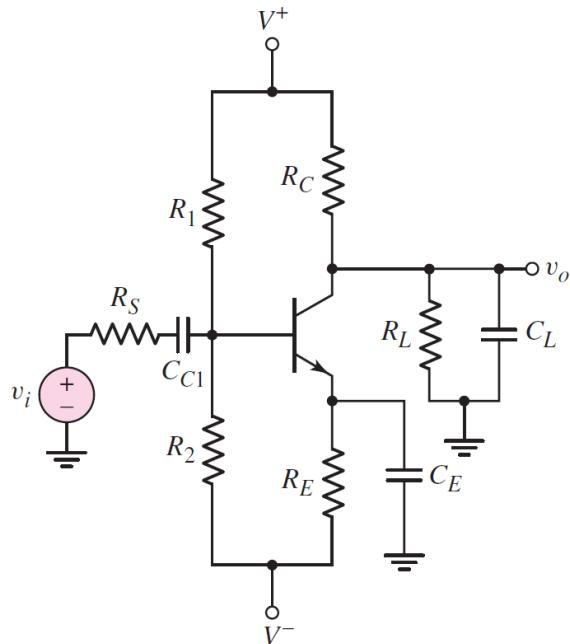
- $R_{eq} = r_\pi \parallel R_B \parallel R_S$
- $C_{eq} = C_\pi + C_M$
- The midband voltage gain magnitude is
  - Assume  $C_\pi$  and  $C_M$  are open circuits

$$|A_v|_M = \left| \frac{V_o}{V_i} \right|_M = \frac{g_m R'_L}{r_\pi \parallel R_B + R_S}$$



# Example 7.7

Determine the upper corner frequency and midband gain of a common-emitter circuit. The circuit parameters are  $V^+ = 5$  V,  $V^- = -5$  V,  $R_S = 0.1$  k $\Omega$ ,  $R_1 = 40$  k $\Omega$ ,  $R_2 = 5.72$  k $\Omega$ ,  $R_E = 0.5$  k $\Omega$ ,  $R_C = 5$  k $\Omega$  and  $R_L = 10$  k $\Omega$ . The transistor parameters are  $V_{BE}(\text{on}) = 0.7$  V,  $\beta = 150$ ,  $V_A = \infty$ ,  $C_\pi = 35$  pF, and  $C_\mu = 4$  pF.



# Common-Source Circuit

- The **high-frequency response** of the common-source circuit is similar to that of the common-emitter circuit
  - $C_\pi$  is replaced by  $C_{gs}$
  - $C_\mu$  is replaced by  $C_{gd}$
- The high-frequency small-signal equivalent circuit of the **FET** is then essentially **identical** to that of the **bipolar transistor**.

